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OF TECHNOLOGY

# Micromachining

enabling new solutions at  
millimeter and  
submillimeter frequencies

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# Microwave/THz MEMS@KTH

(School of EE and CS)



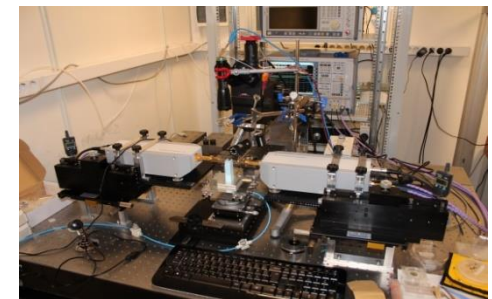
*Group size:*

- 1 professor
- 3 senior researchers
- 10 PhD students

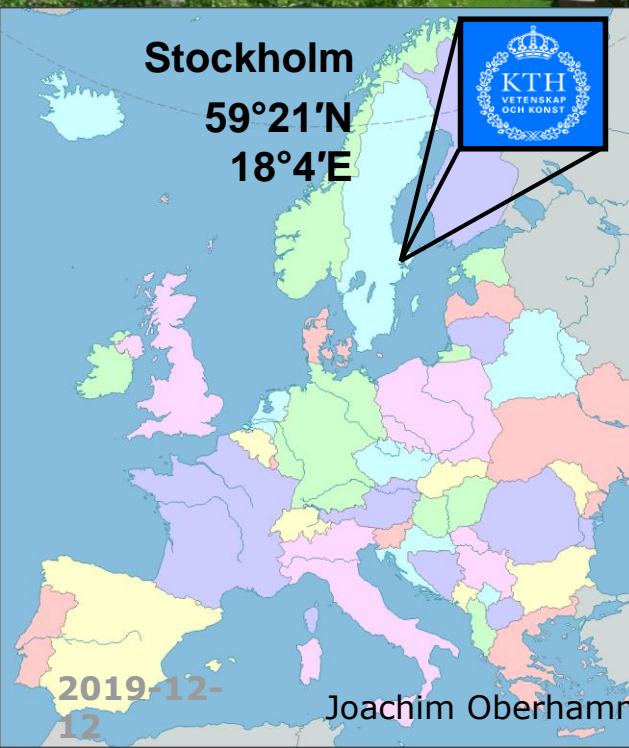
*Average external project funding:*

- >EUR 1 million/year

*KTH micro&THz resources:*



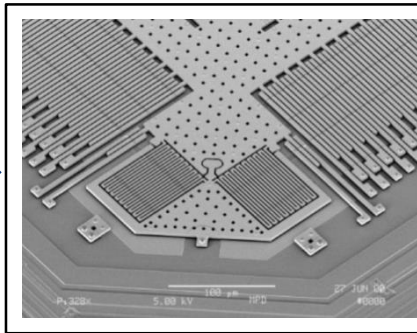
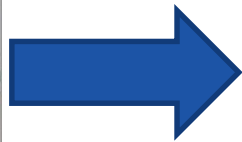
- 1300m<sup>2</sup> class 100 clean-room for MEMS, photonics, III-V, SiC
- MW characterization (VNA, antennas) to 500 GHz



Stockholm  
59°21'N  
18°4'E

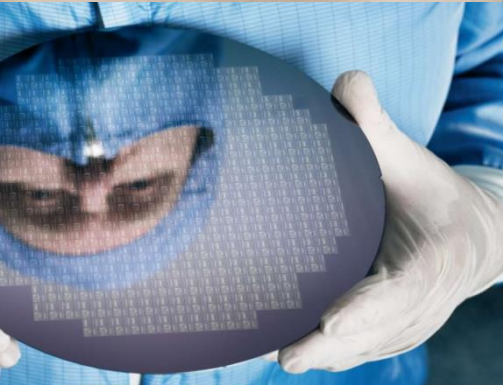
2019-12-12

Joachim Oberhammer



inertial sensors,  
microphones, ...  
billions devices/year,  
<1 EUR/dev

**Revolutionized  
sensors and  
user interfaces**



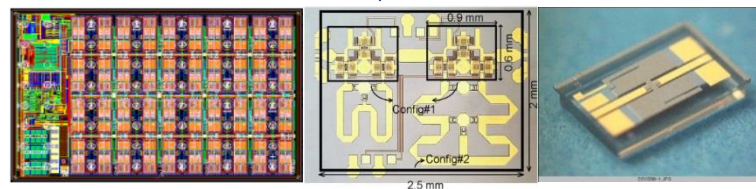
**Semiconductor  
clean-room  
manufacturing:**

- miniaturization
- very high volume
- very low cost

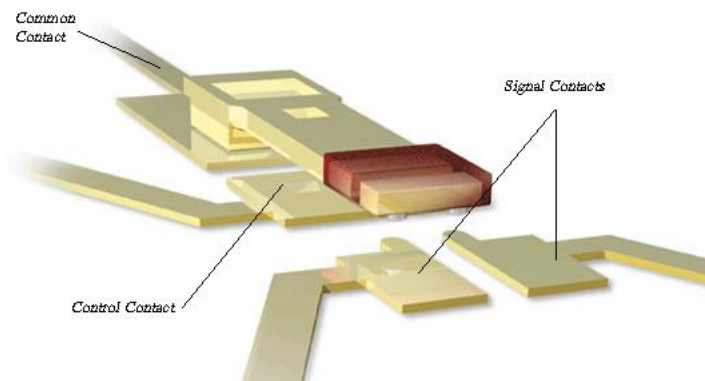
**Revolutionized  
information age**

# Micro-mechanics MEMS

Micro-ElectroMechanical Systems



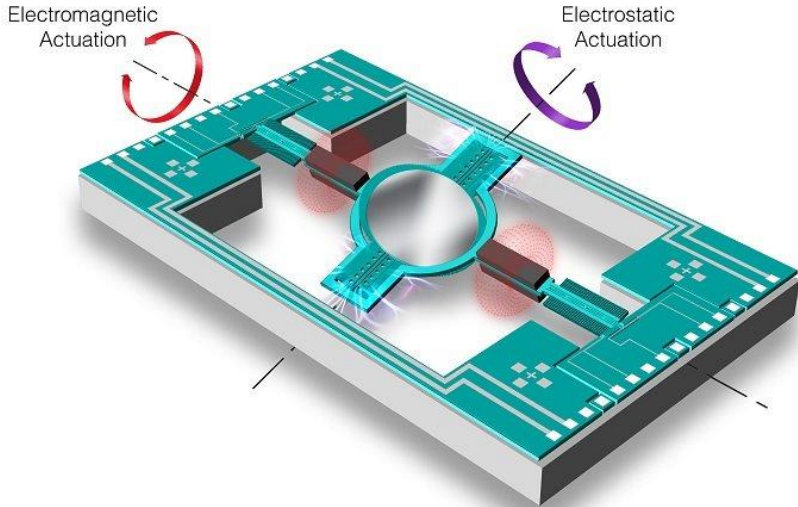
**RF (radio–frequency) MEMS:**  
mobile phone antenna tuners,...



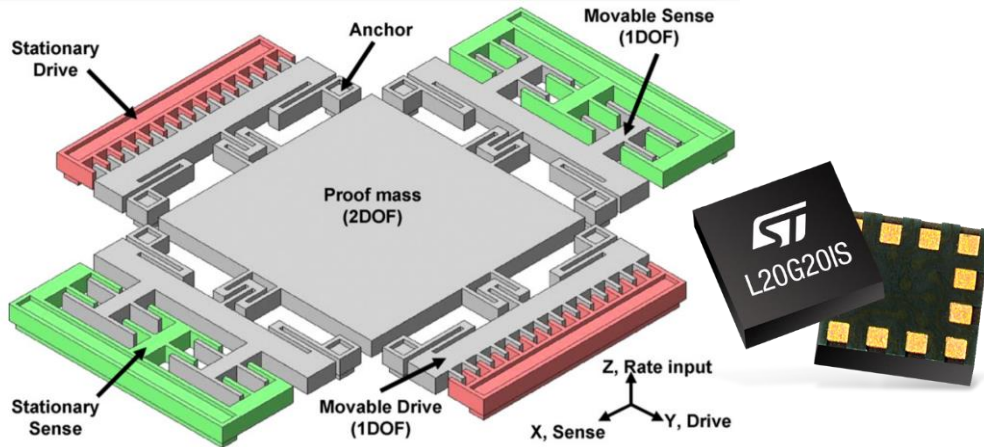
*Typical performance:*

- insertion loss < 0.5dB@38GHz
- isolation: 23dB@10GHz, 18dB@36GHz
- linearity IIP3 > 65dBm

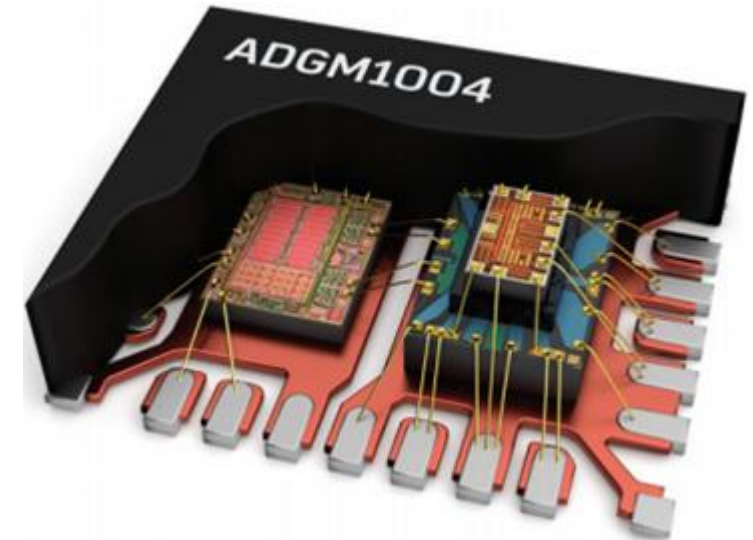
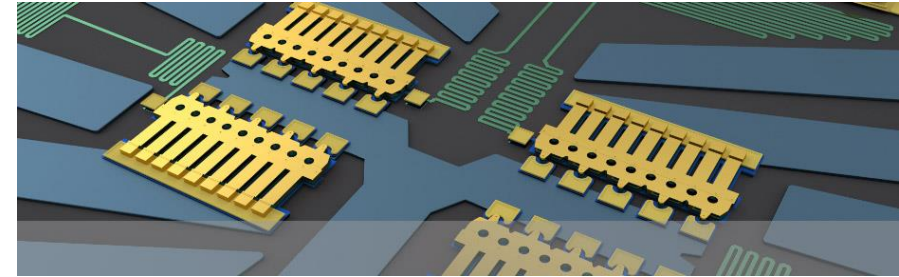
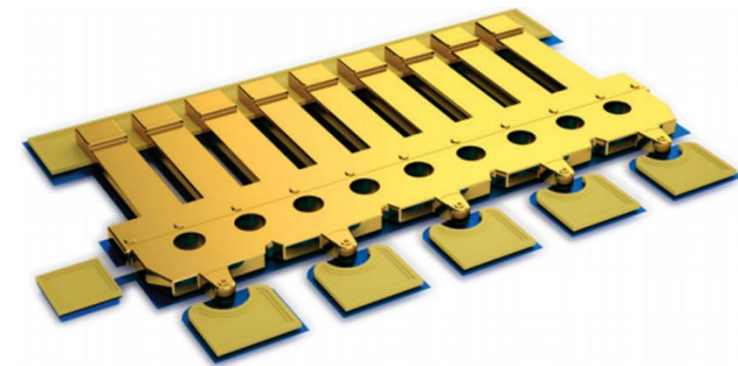
# MEMS examples ...



Moveable micromirror for LIDAR



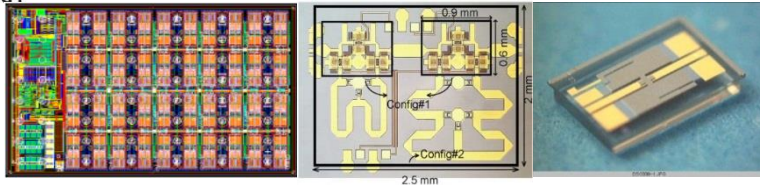
MEMS gyroscope



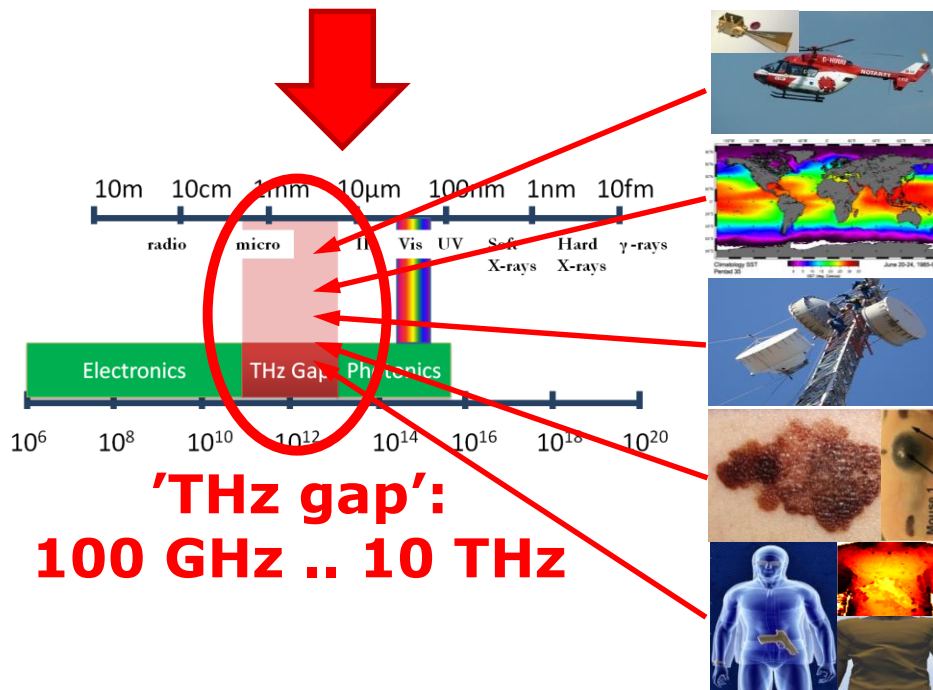
Analog devices SP4T MEMS switch:  
 13 GHz BW, IL 0.45 dB (2.5 GHz),  
 ISO 30 dB (1GHz)  
 3.4 billion cycles (hot switched, 10 dBm)

# From RF MEMS to THz MEMS ...

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**RF (radio–frequency) MEMS:**  
mobile phone antenna tuners,...



**? THz MEMS revolutionizing exploitation of THz spectrum ?**

microwave geometries are 3D

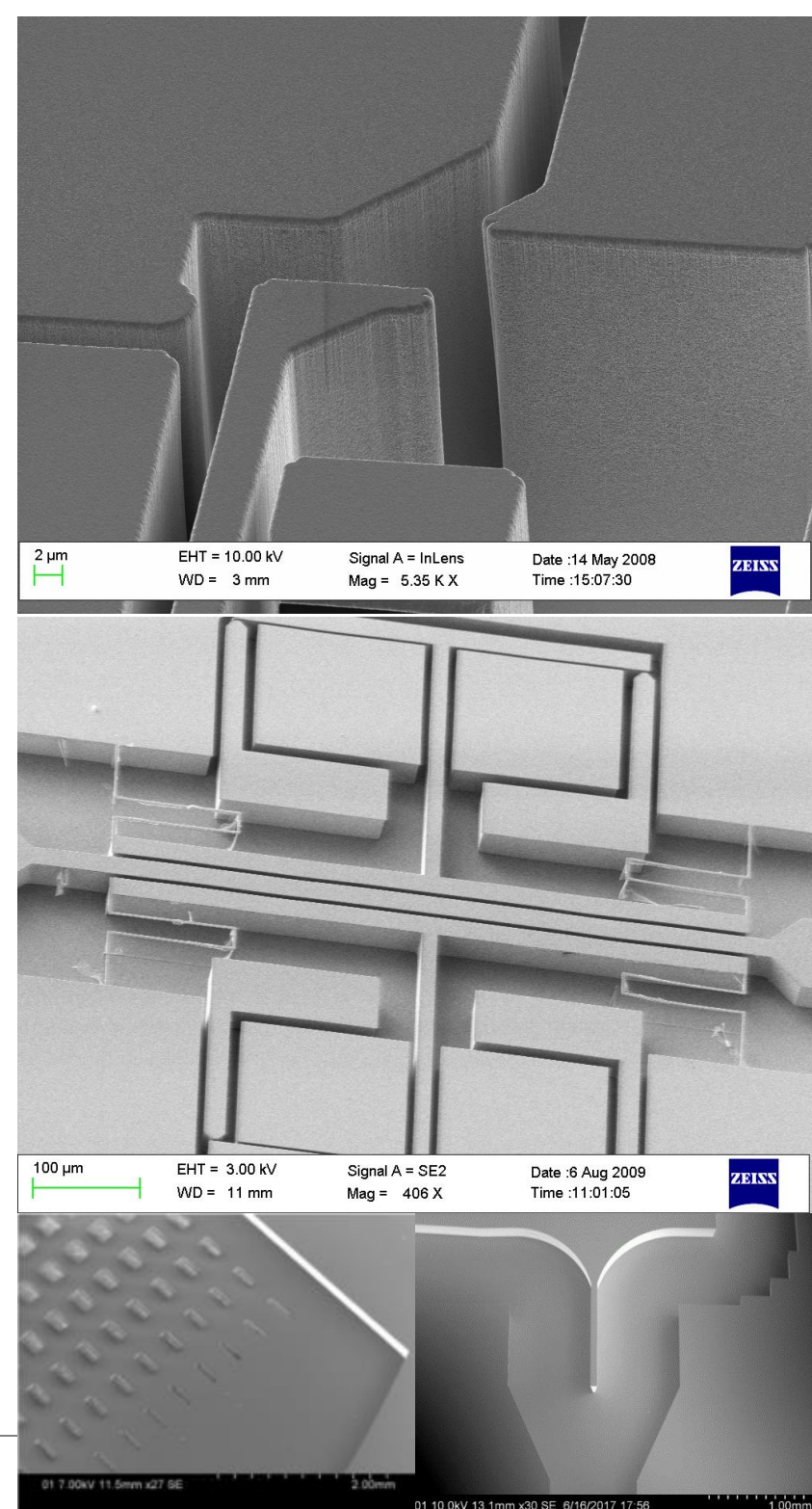
3D-micromachining

3D micromachined waveguides

# Why micromachining?

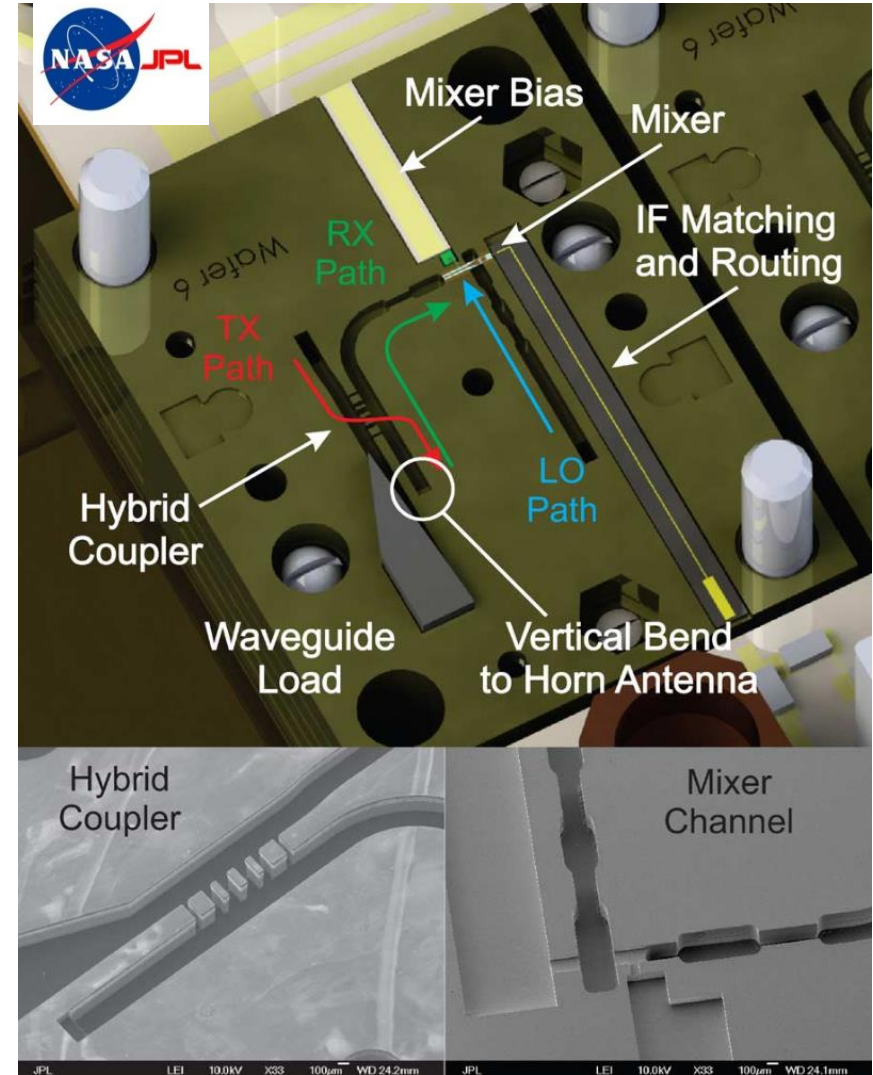
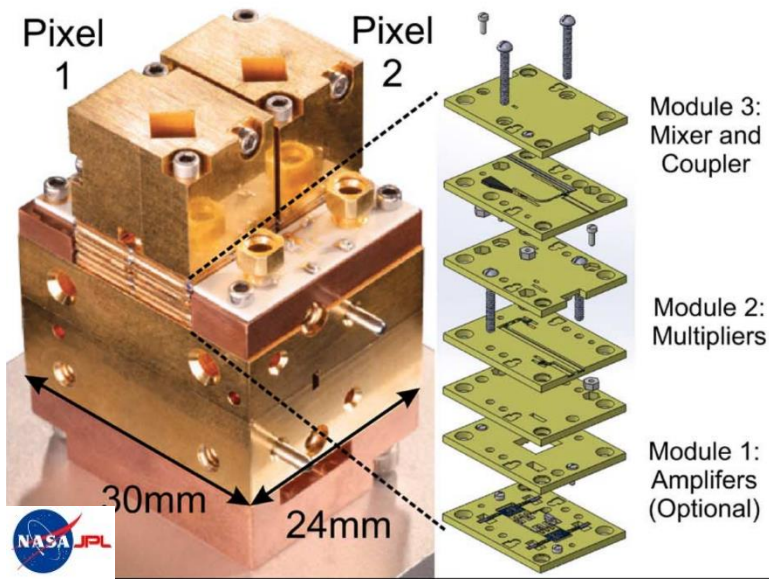
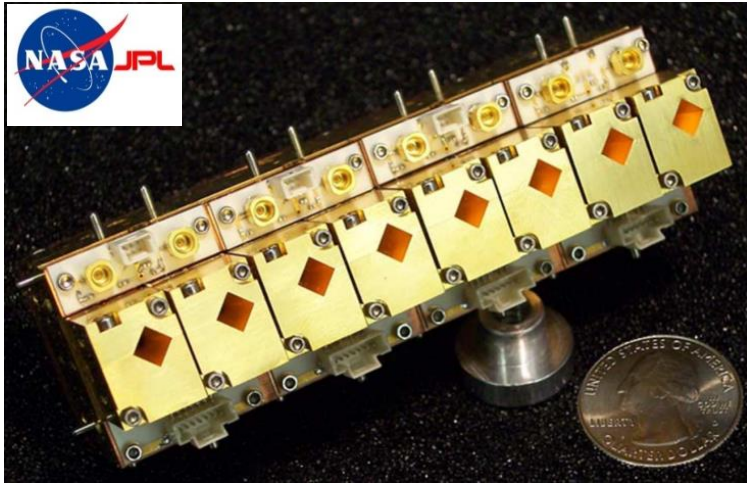
- Feature sizes/tolerances: down to  $\mu\text{m}$   
=> accurate geometries for THz-wavelengths
- Surface roughness: down to nm  
=> ultra-low insertion loss
- Ultra-high aspect ratio geometries:
  - Vertical features: 110:1
  - Horizontal features: 1000:1
- Alignment accury:  $<2 \mu\text{m}$
- Volume manufacturable
- High product uniformity
- Low cost in high volumes
  
- Integrated MEMS microactuators  
=> reconfigurability  
with near-ideal performance

## Micro electro mechanical systems

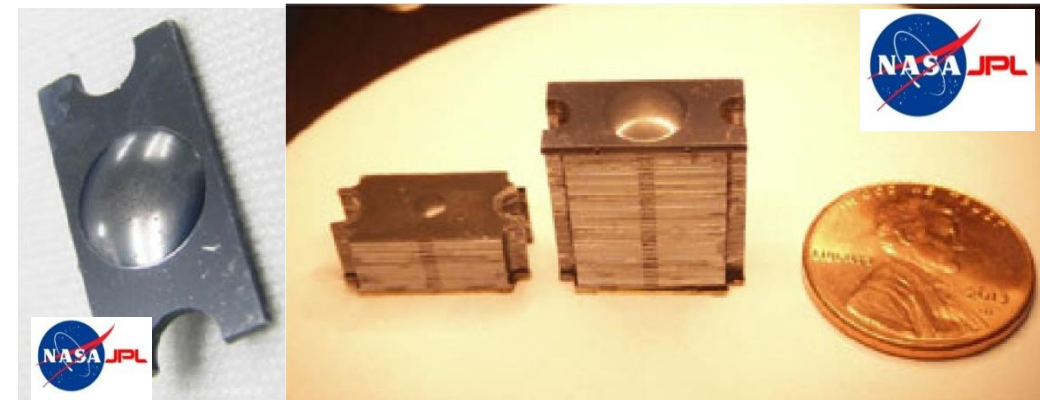
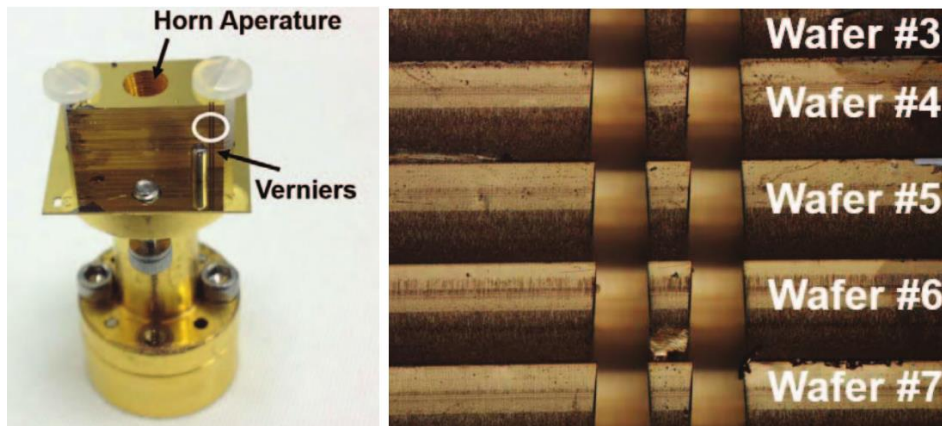
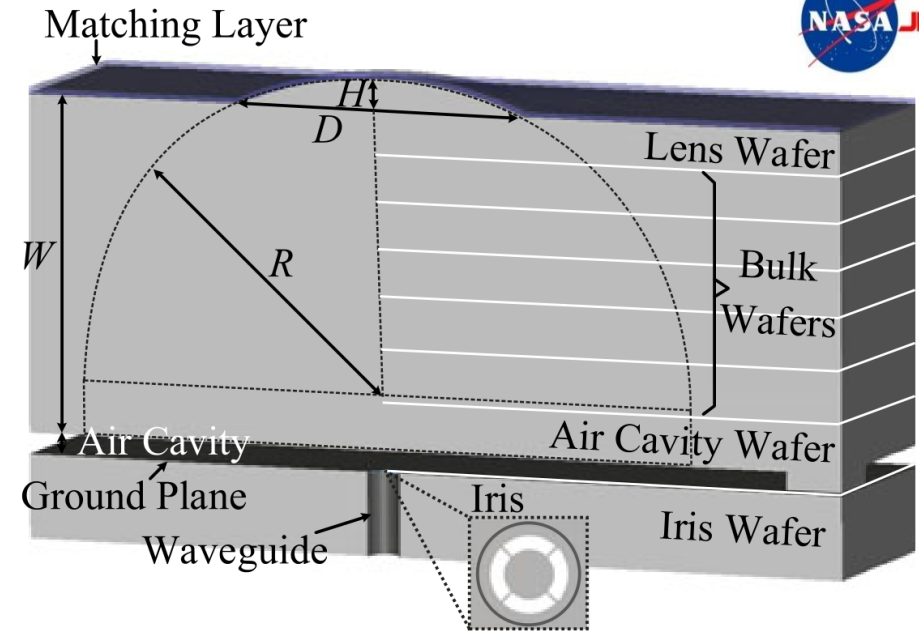
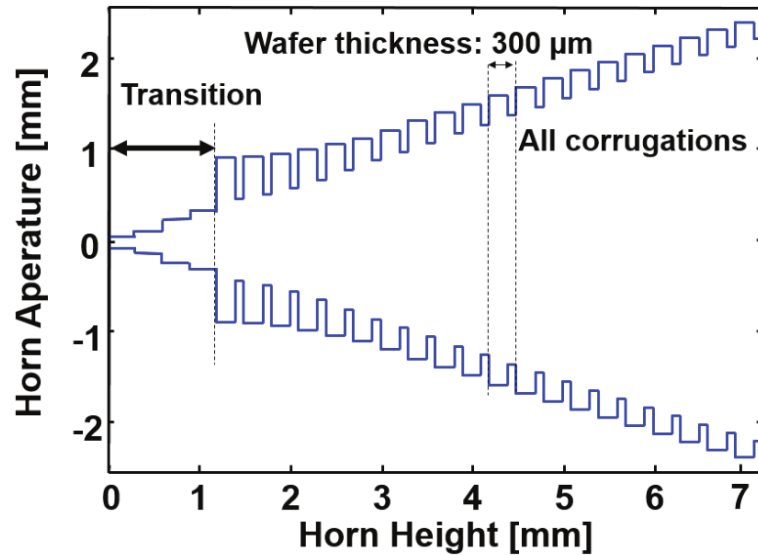


# State-of-the-art THz microsystems: 340 GHz 8-pixel transceiver for imaging radar (JPL)

[T-THzSciTec 2015]



# Micromachined THz stacked-chip antennas by JPL



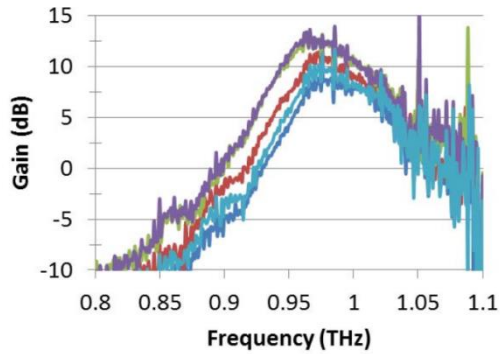
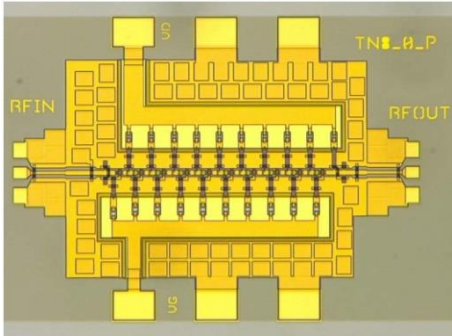
By 24 stacked micromachined silicon chips, 340 GHz, 20 dBi gain [JPL, 2015]

1.9 THz, narrow-band lens antenna [T-THzSciTec 2017]

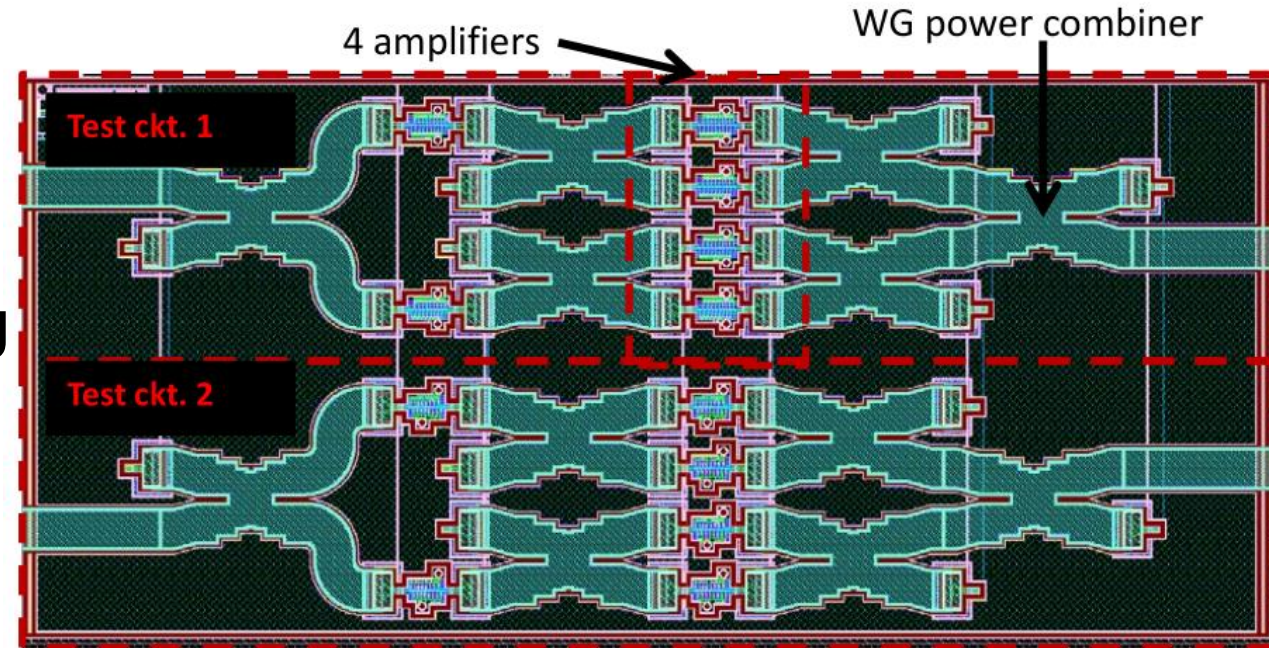
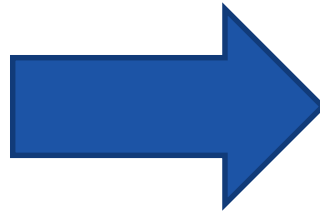


# Power-combining at 1 THz

## Integrated 4-way Power Combiner

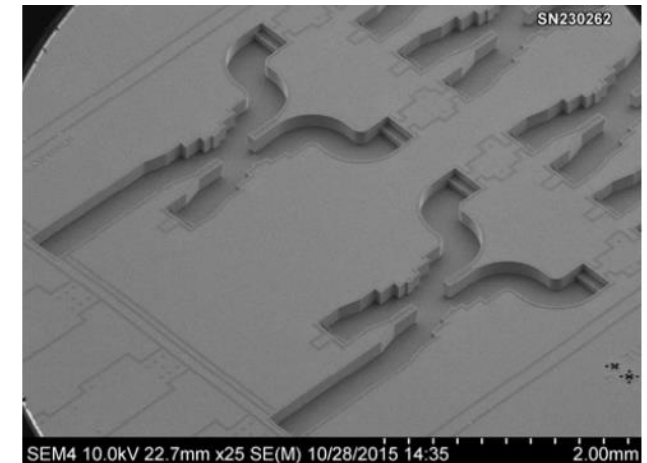
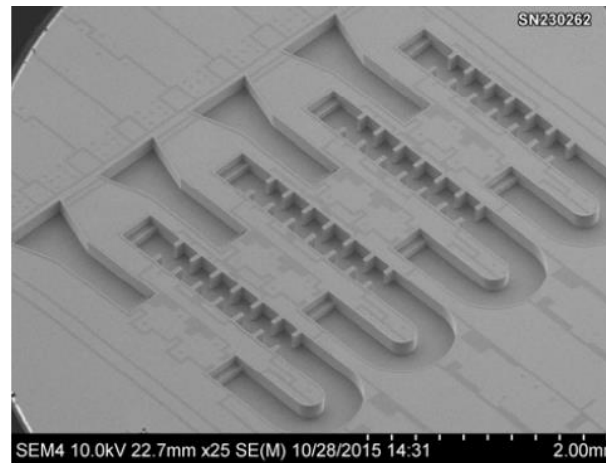


**Micro-machining**

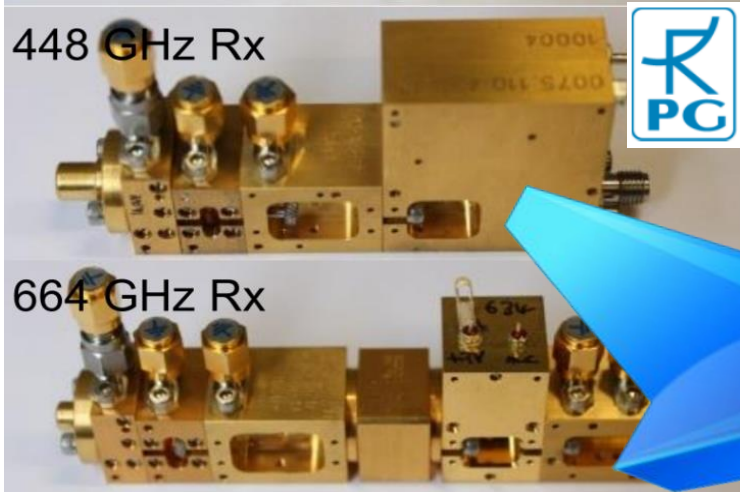


**0.4 mW Measured Power at 975 GHz**

- Split block housings proven effective, *but*
- Expensive and difficult to mass produce



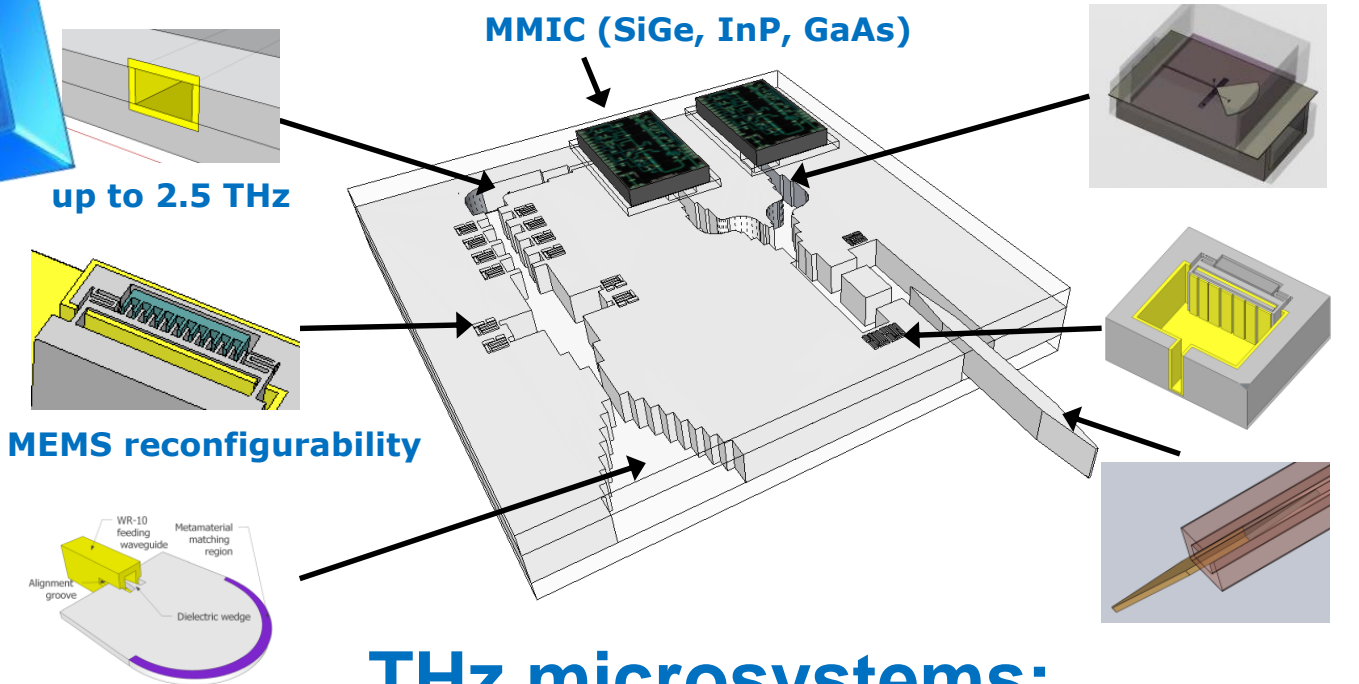
# Micromachining & MEMS enabling new ways of building THz components and systems



1000x smaller  
 1000x lighter  
 100x lower cost  
 10x less power consumption  
 reconfigurable  
 volume-manufacturable

## THz technology = stone age

- bulky
- heavy
- manually assembled
- expensive
- only for scientific instruments
- not volume manufacturable

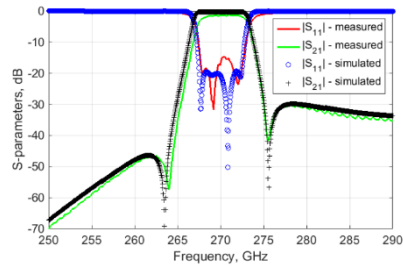


**THz microsystems:**  
 Enabling the large-scale exploitation  
 of the THz frequency spectrum

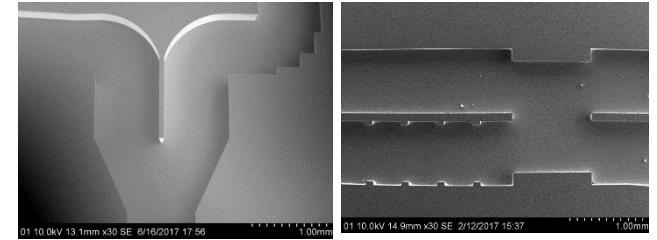
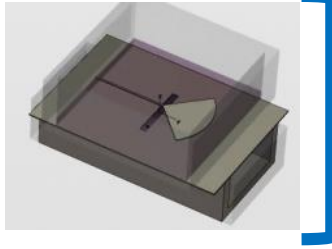
# Micromachined THz Systems at KTH

Low loss waveguides:

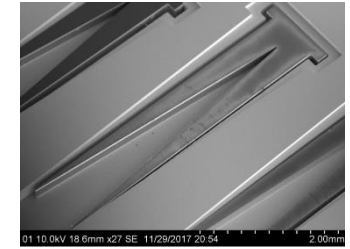
0.020 dB/mm @ 270 GHz  
0.008 dB/mm @ 170 GHz



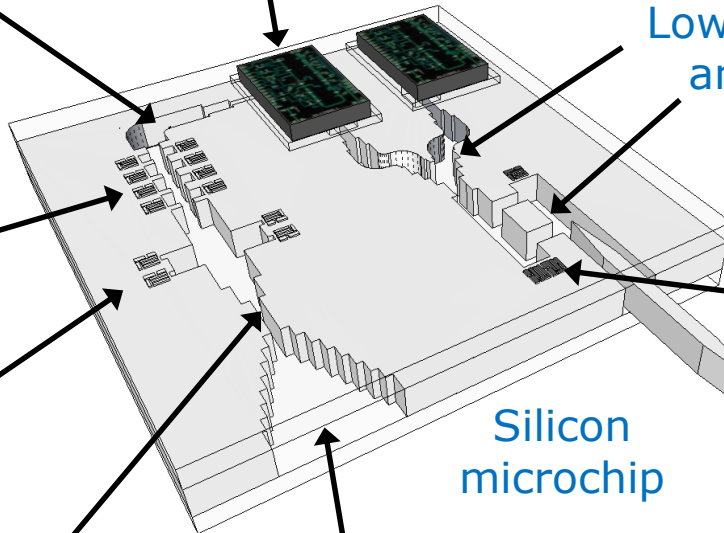
MMICs (SiGe, InP, GaAs) with waveguide interfaces



Low loss waveguide power combiners and couplers (0.2dB IL@320GHz)

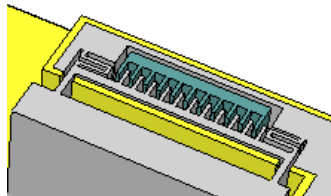


Integrated waveguide absorbers

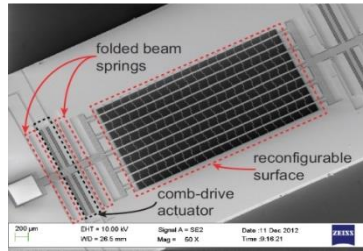


Silicon microchip

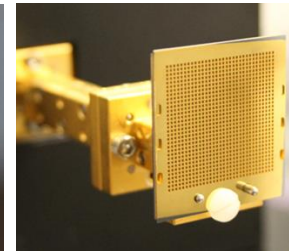
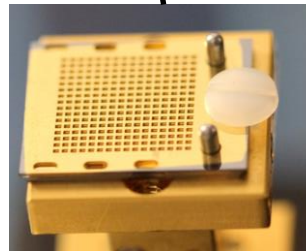
Filters:  $Q=800@450\text{GHz}$ ,  
 $Q=1600@170\text{GHz}$



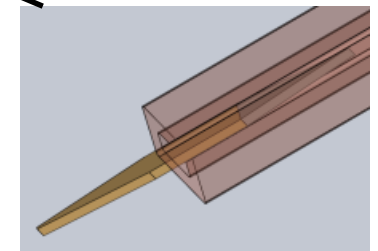
MEMS phase shifters up to 750GHz



MEMS waveguide switches:  
220GHz: 50dB ISO, 0.6dB IL



Antenna arrays, 320-400 GHz:  
16x16: 34dBi gain, 0.8dB IL  
32x32: 38dBi gain, 1.4dB IL

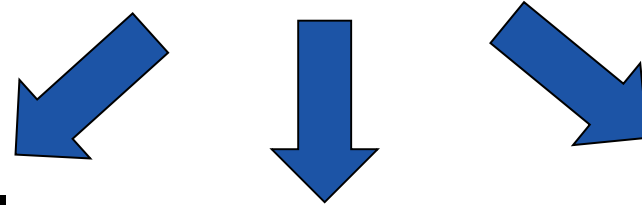


Micromachined medical sensor interfaces



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# Combining competences in

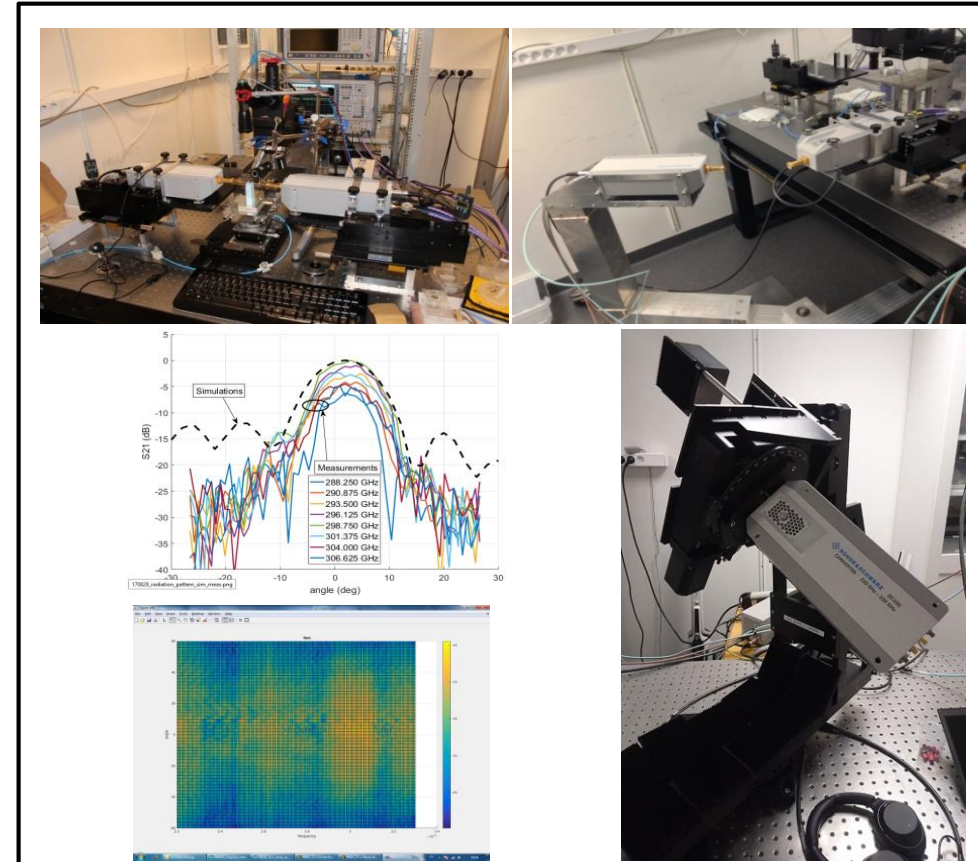
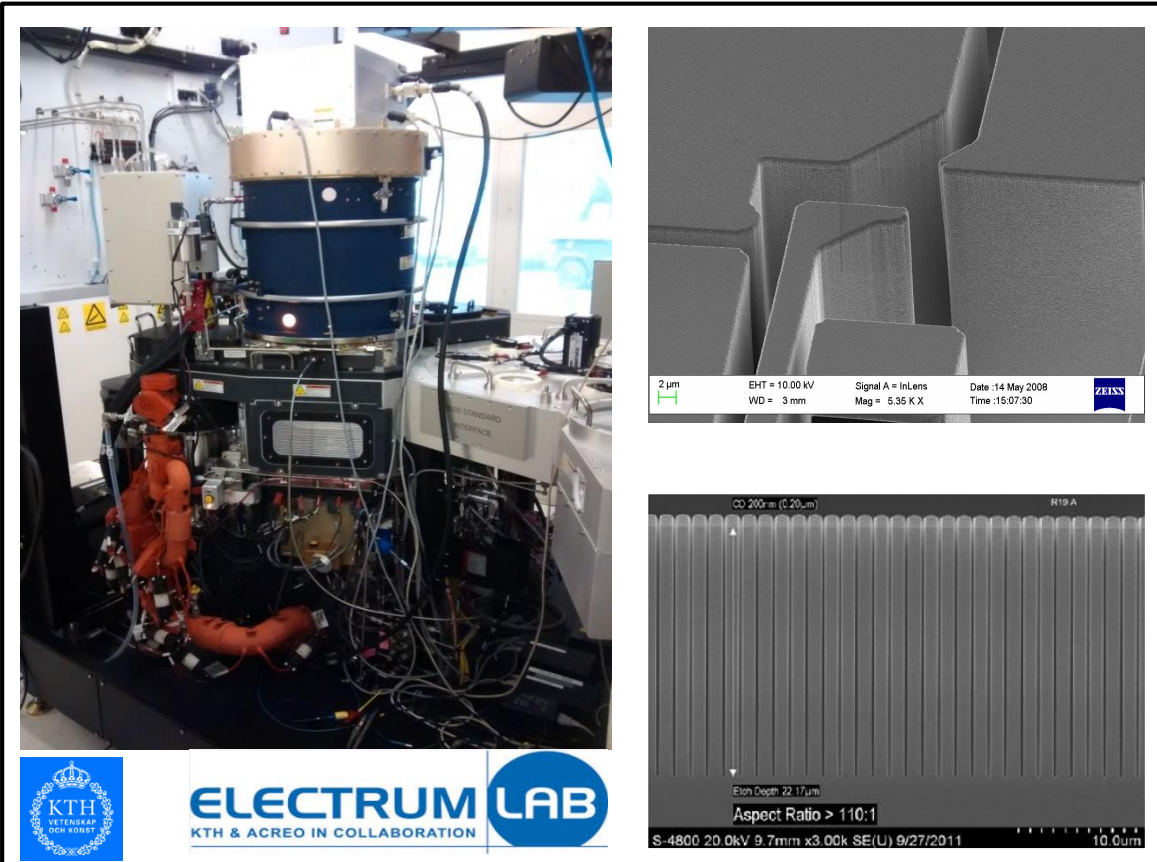


## Advanced micro-wave design

## Advanced silicon micromachining

## Measurements & characterization

- VNA 67-500 GHz
- Antenna robot (4DoF) 67-500 GHz



**ELECTRUM LAB**  
KTH & ACREO IN COLLABORATION

# Examples of sub-THz micromachined/MEMS devices recently implemented at KTH (since 2015)



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## *Basic components:*

- Waveguides
- Couplers, splitters, matched loads
- Waveguide switches, phase shifters
- Ultra high-Q filters

## *Complex components:*

- Orthomode transducers
- Antenna arrays

## *Systems:*

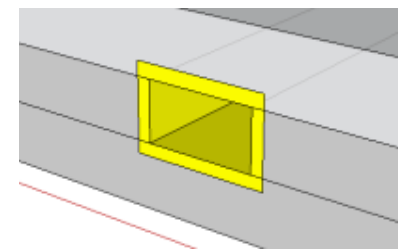
- Telecom front-end integration platform
- Beam-steering/radar demonstrators



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# ***Micromachined waveguides***

# Ultra-low loss micromachined waveguides at 110-330 GHz



## 220-330 GHz:

0.020-0.070 dB/mm

$Q_{UL} \sim 750-800$  (270 GHz)

[IEEE THzSciTec 2018]

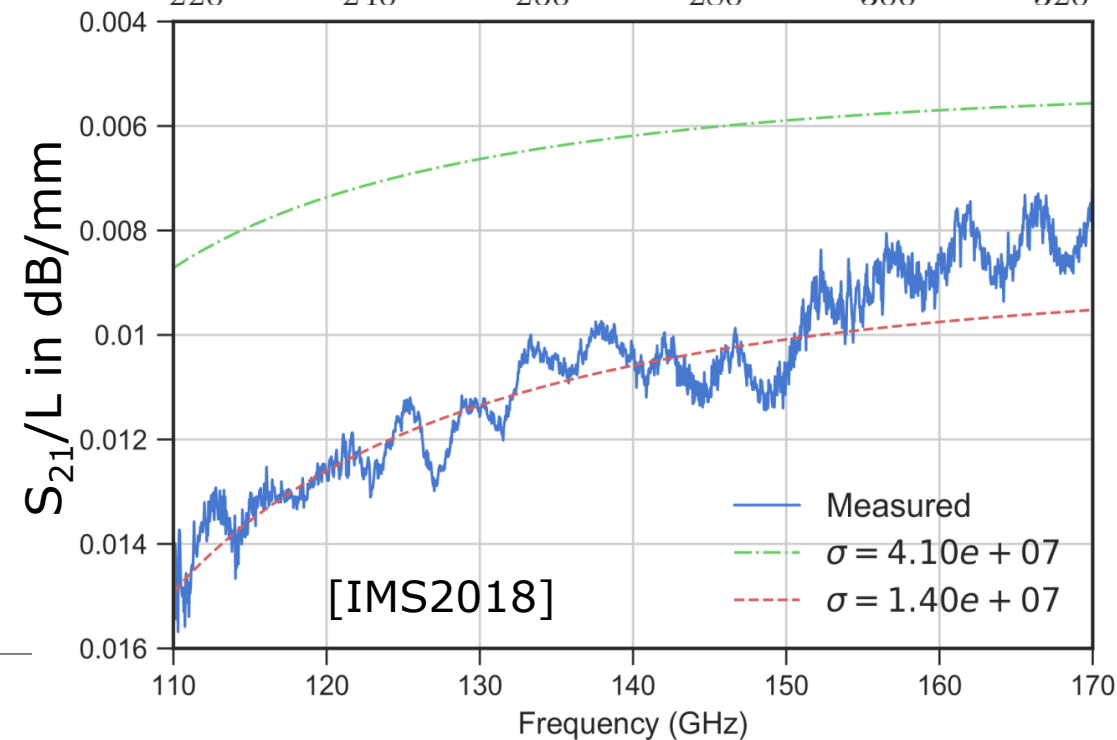
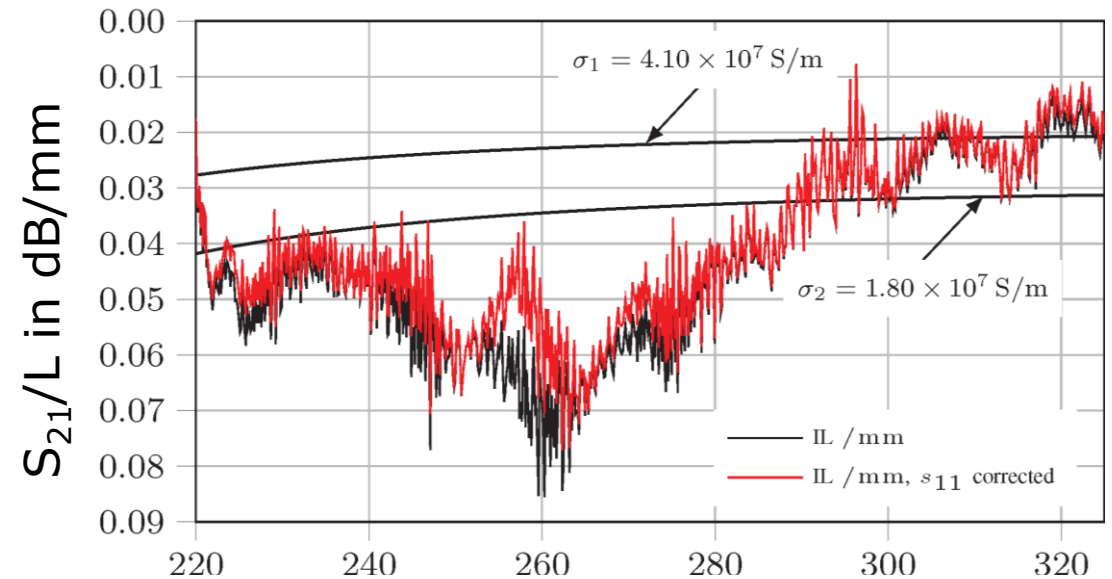
**Best performance of any waveguide in any technology in these bands!**

## 110-170 GHz:

0.008-0.016 dB/mm

$Q_{UL} \sim 1600$

[IEEE IMS 2018]



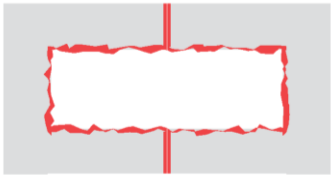
# Ultra-low loss micro-machined waveguides

$$\alpha_c = \alpha_{c0} (1 + K_{rough})$$

$$K_{rough} = \frac{2}{\pi} \tan^{-1} \left[ 1.4 \left( \frac{R_a}{\delta} \right) \right]$$

$$\alpha_{c0} = 4.58 \times 10^{-8} \sqrt{\frac{f}{\sigma}} \left[ \frac{2 \frac{b}{a} \left( \frac{f_c}{f} \right)^2 + 1}{b \sqrt{1 - \left( \frac{f_c}{f} \right)^2}} \right] \text{ dB/mm}$$

## Conventional approaches:

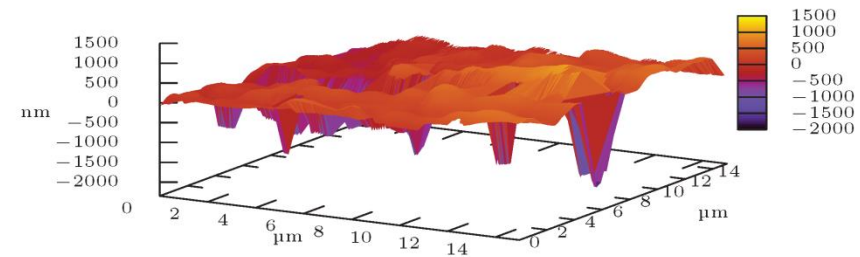


E-plane split

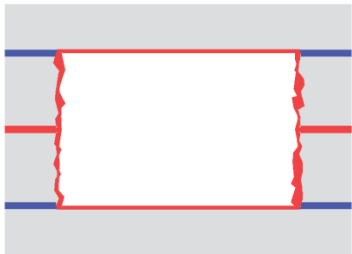


Single H-plane split

(a) waveguide sidewall



## New approach: Double H-plane split



**110-170 GHz:**

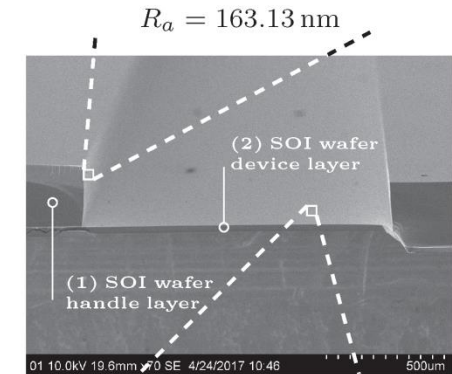
0.008-0.016 dB/mm

$Q_{UL} \sim 1600$

**220-330 GHz:**

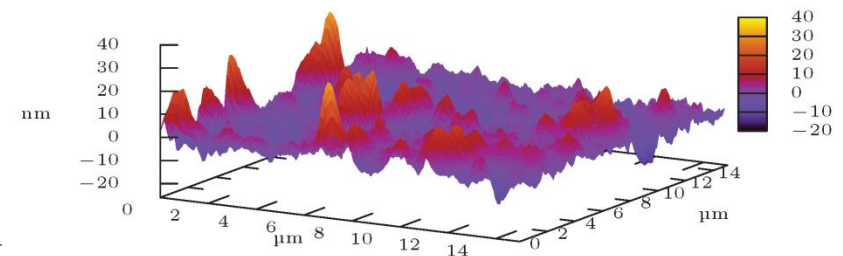
0.020-0.070 dB/mm

$Q_{UL} \sim 750-800$



$R_a = 163.13 \text{ nm}$

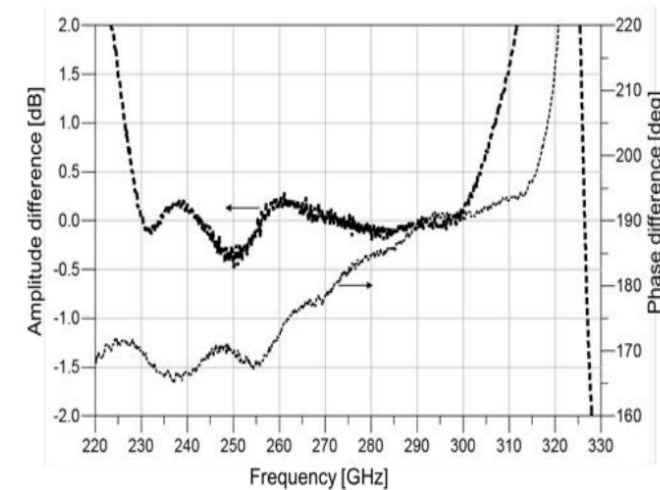
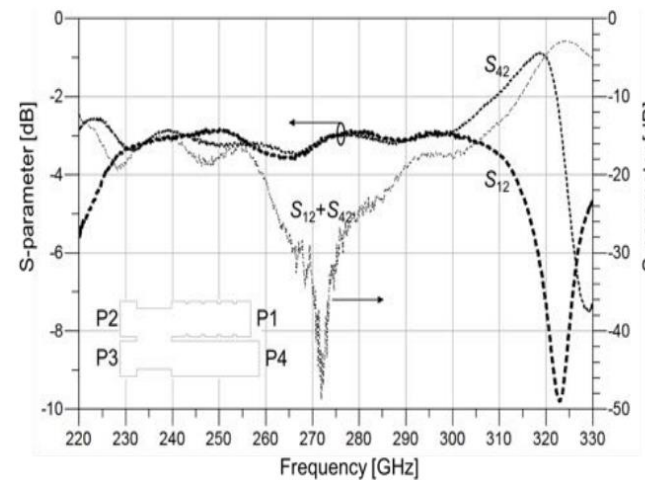
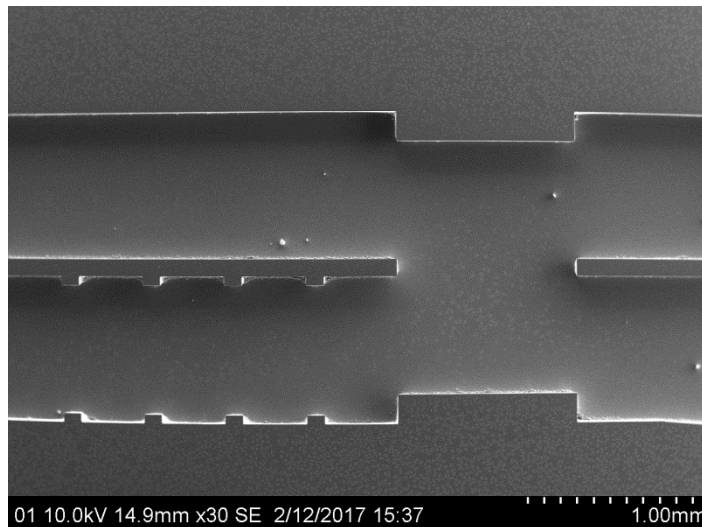
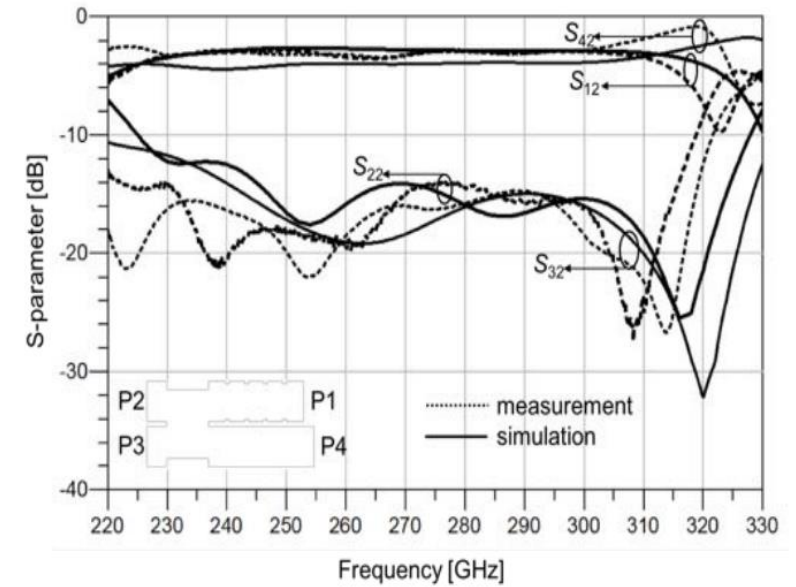
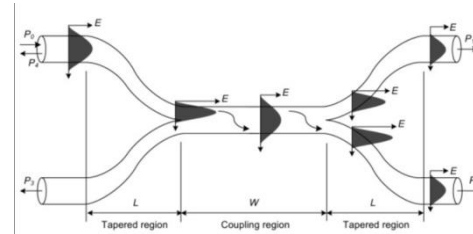
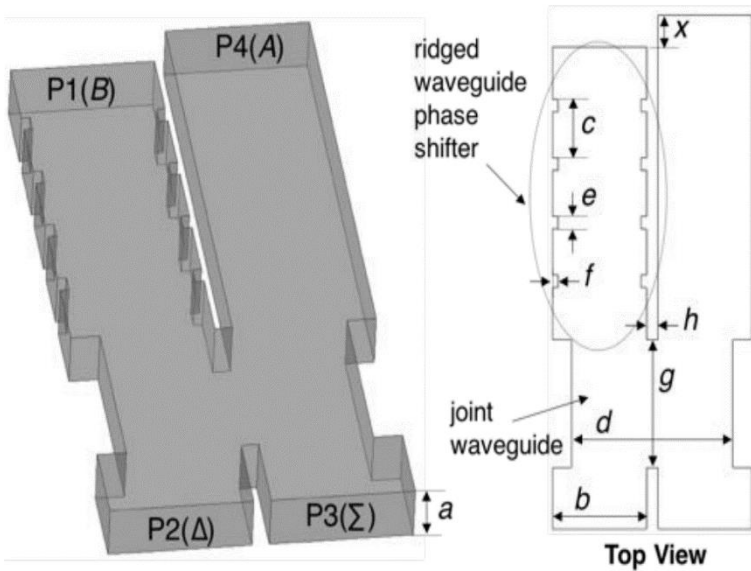
$R_a = 2.14 \text{ nm}$



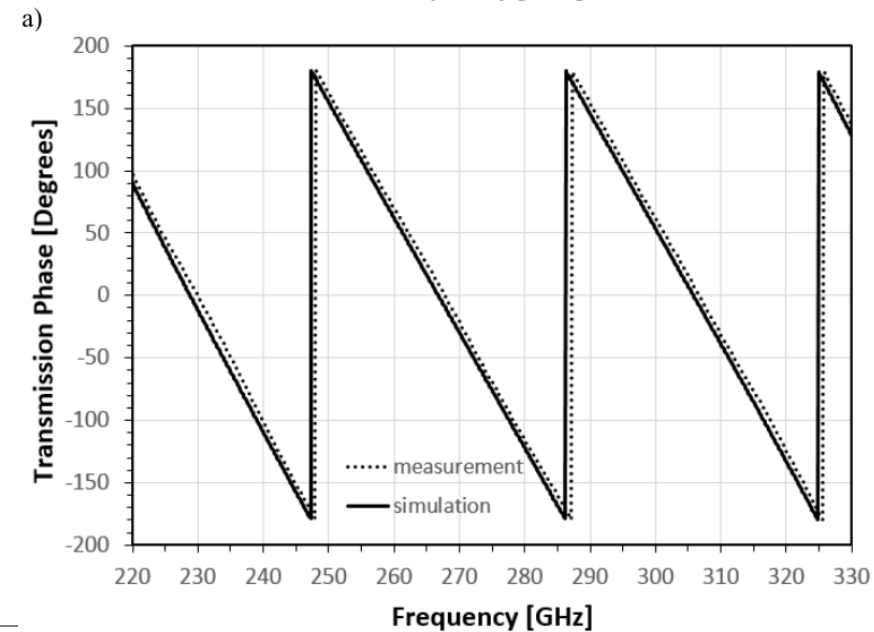
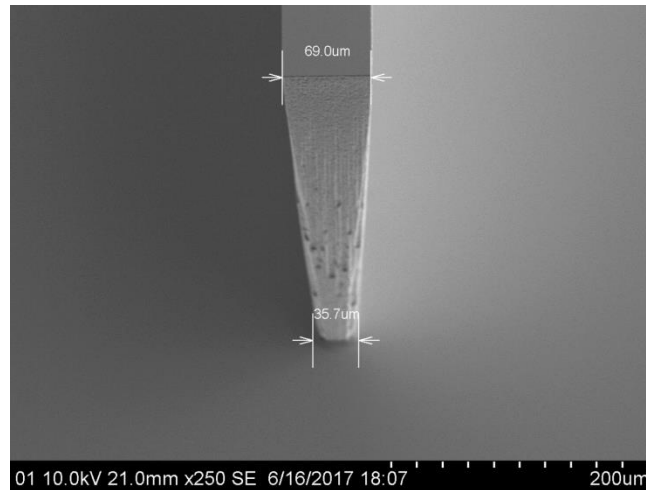
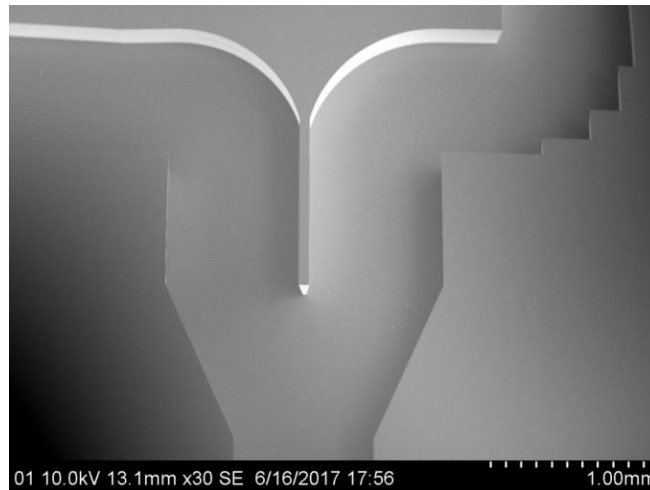
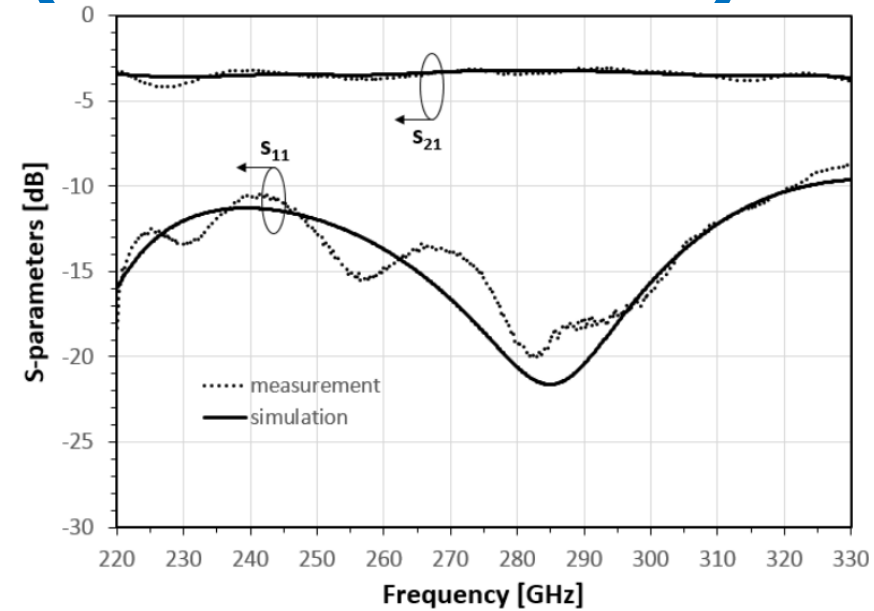
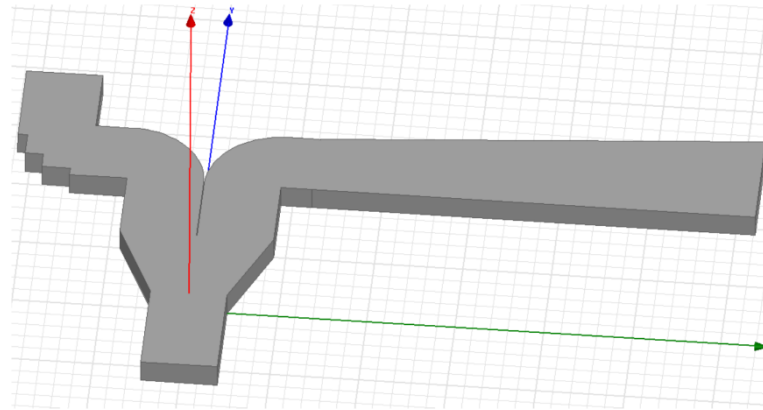
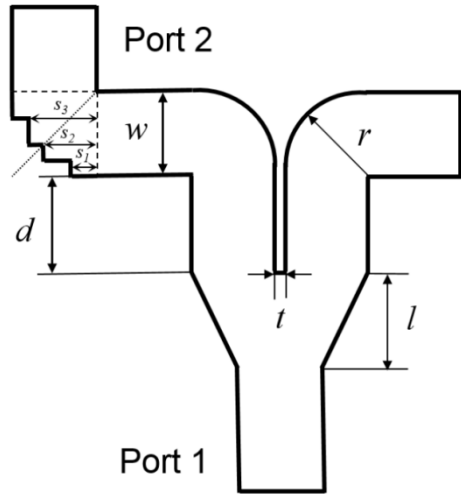
(b) waveguide top and bottom



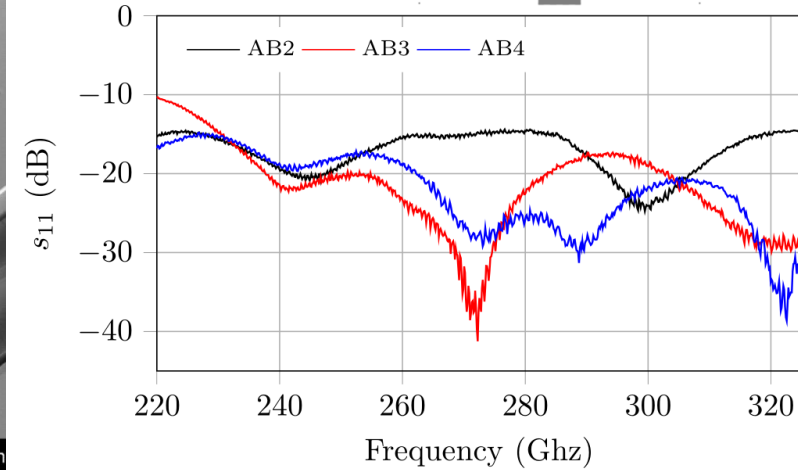
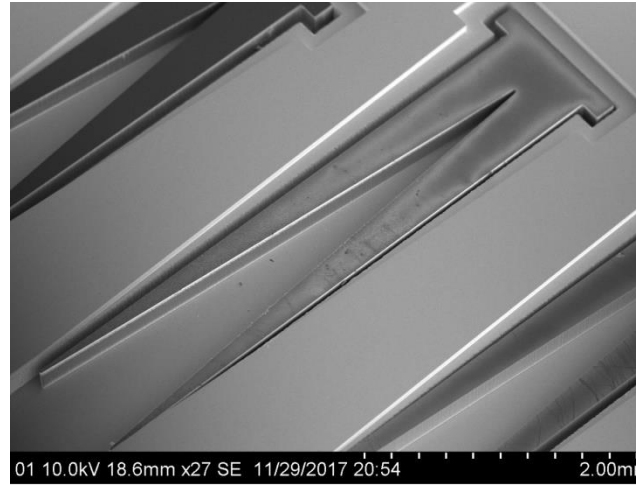
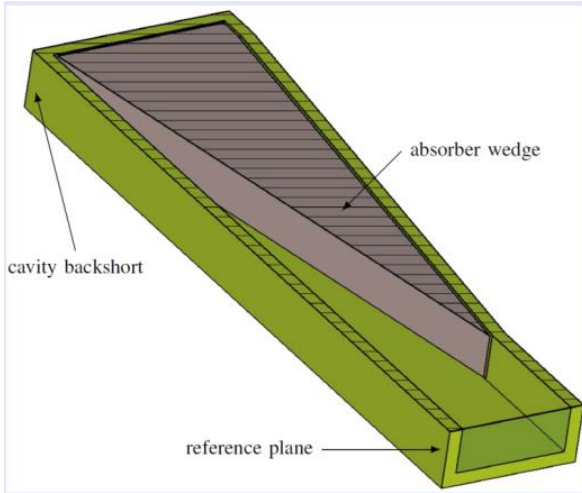
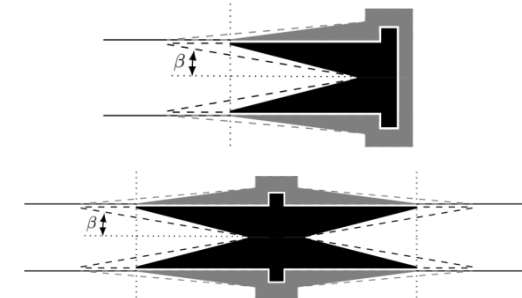
# Ultra-low loss micromachined 3-dB coupler at 220-330 GHz



# Ultra-low loss micromachined power splitter (220-330 GHz)

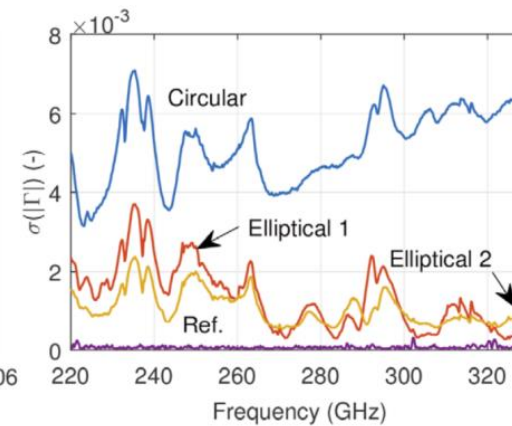
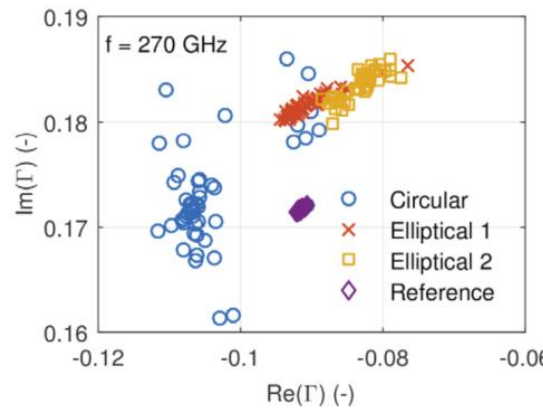
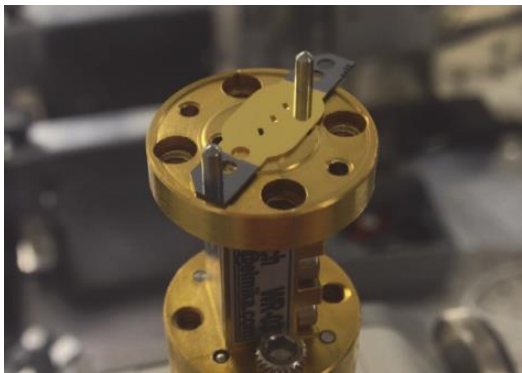


# Interfaces & measurement technology



On-chip integrated absorbers, calibration kits

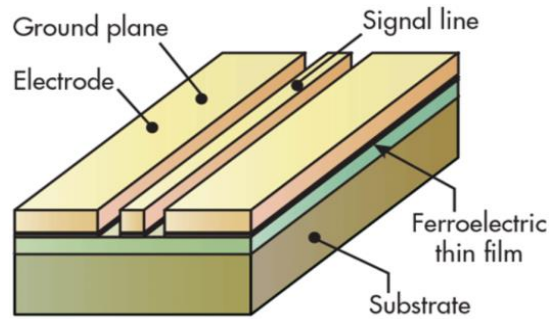
[EuMC 2017, IMS 2018]



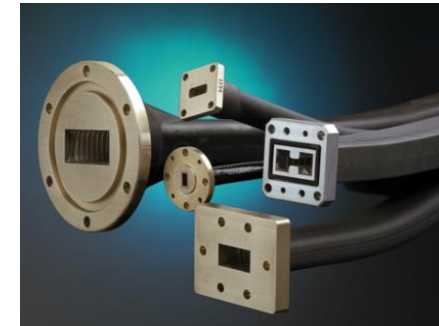
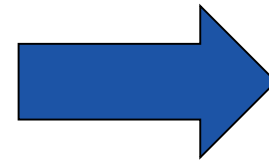
Measurement interfaces:  
High-precision flange to microchip alignment method

[IEEE IMS 2017]

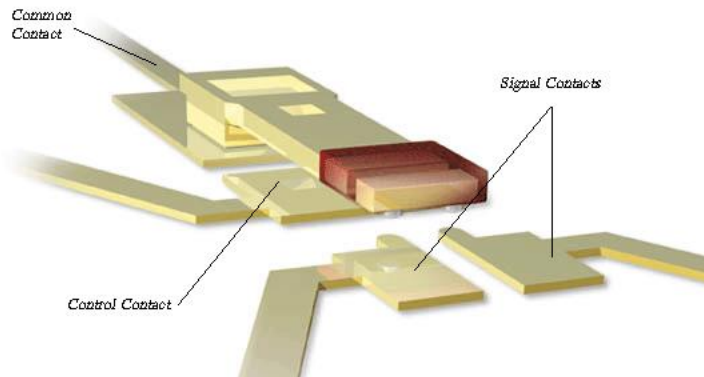
# MEMS waveguide switches



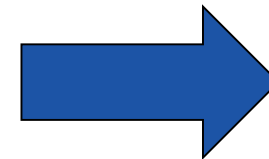
**Transmission lines**



**waveguides**

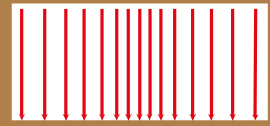


**RF MEMS planar switch**

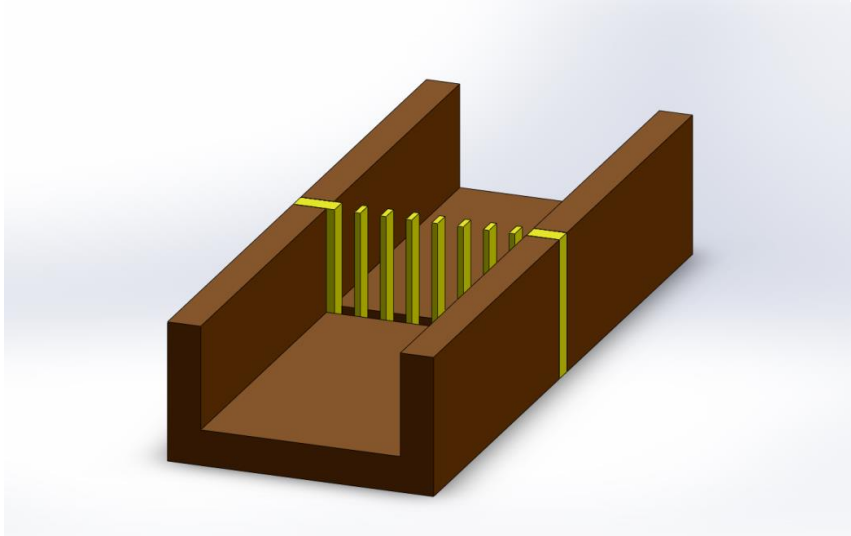


**MEMS waveguide switch**

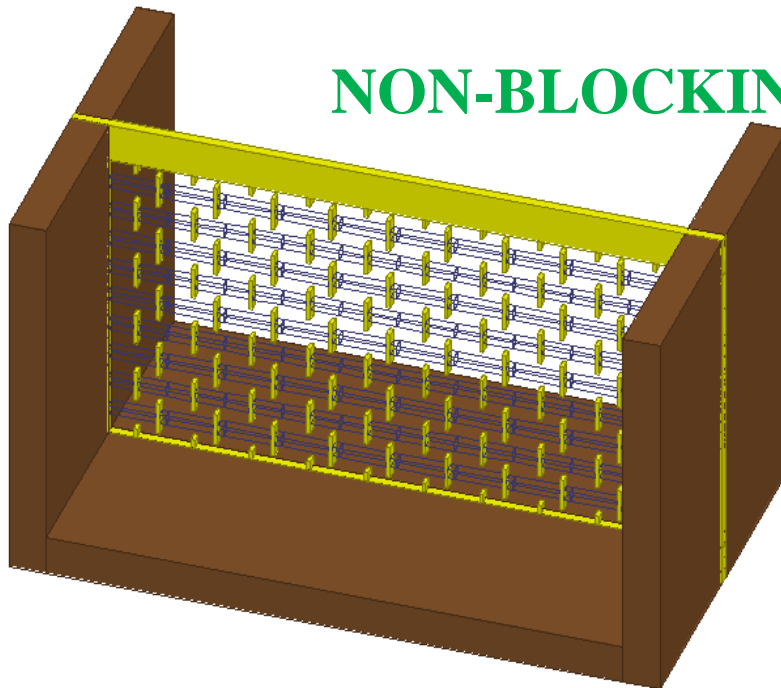
# How to build a MEMS waveguide switch?



TE10 mode

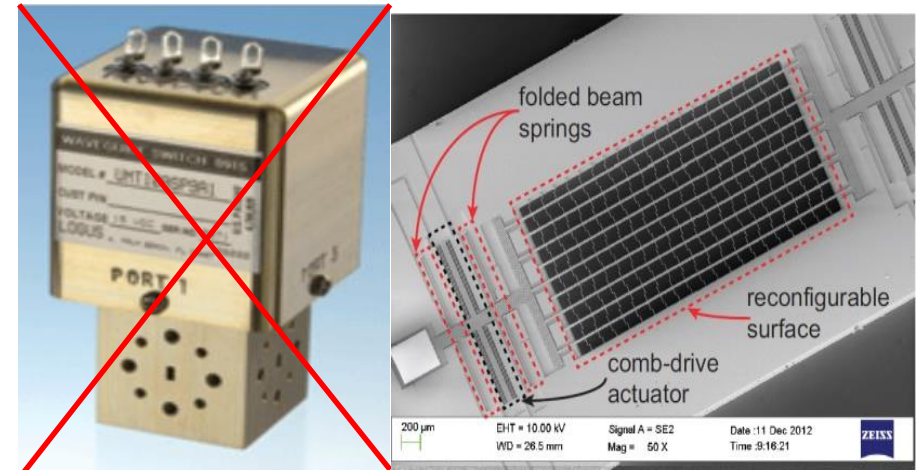


**NON-BLOCKING**



## MEMS:

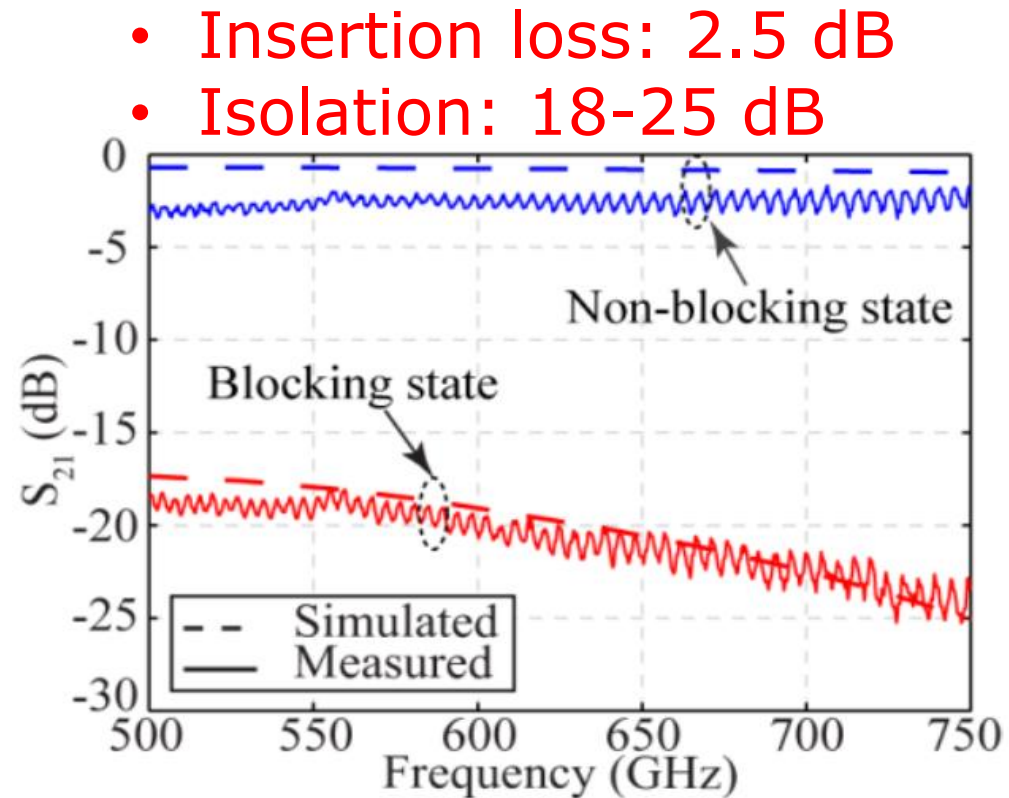
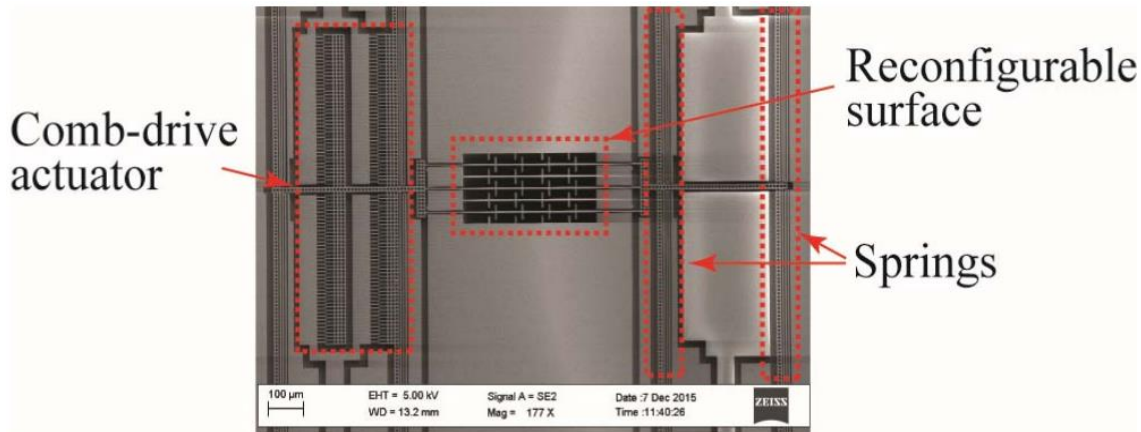
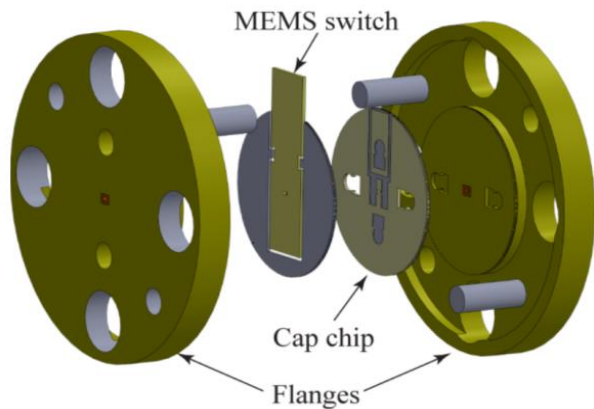
- 100 000 x smaller
- 100 000 x lighter
- 10 000 x faster
- equal performance



**30 μm thick!  
thinner than a hair**

# 500-750 GHz MEMS waveguide switch

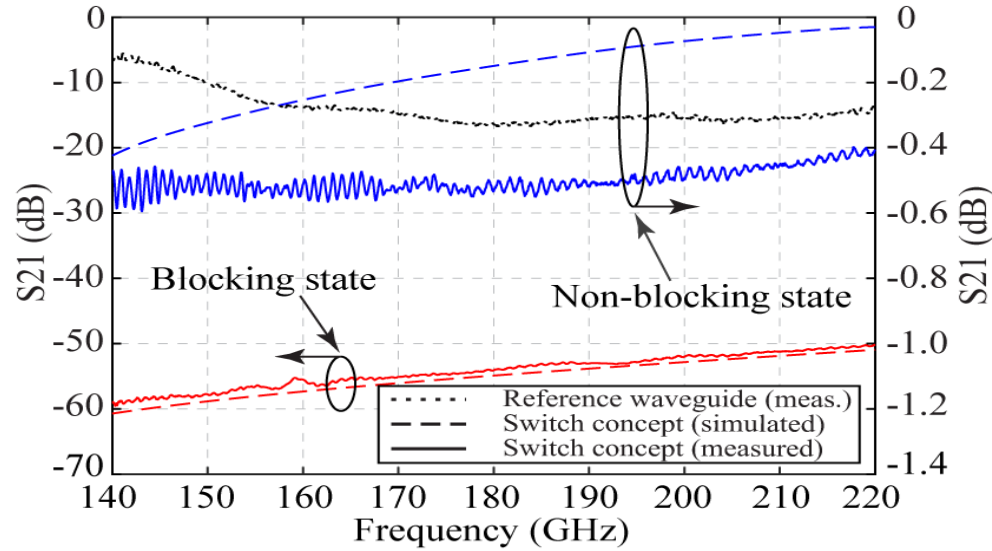
- First MEMS waveguide switch above 70 GHz
- First sub-mm-wave MEMS switch
- First MEMS switch above 220 GHz



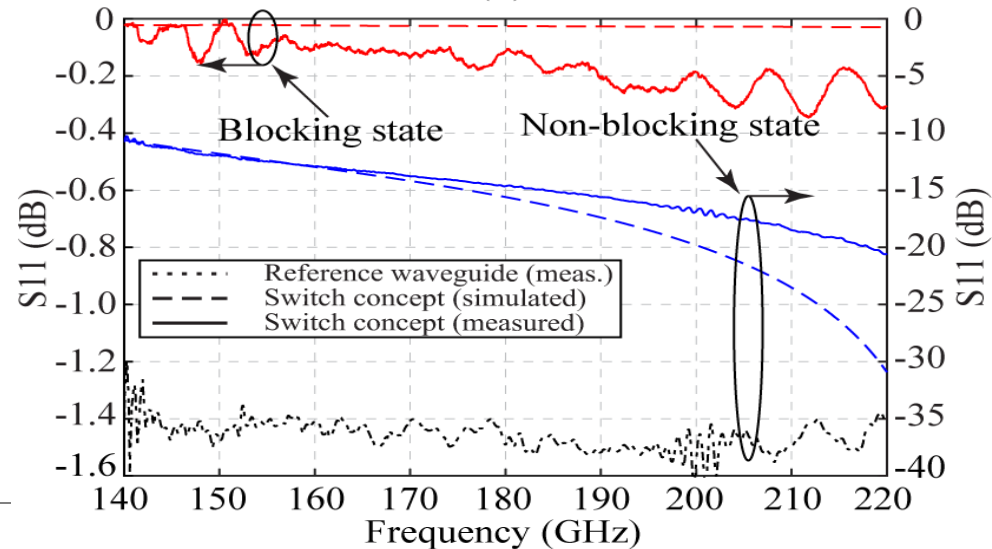
[IEEE IMS 2016, IEEE THzSciTec 2017]

# High on/off ratio 183 GHz switch for radiometer calibration

## Prototype measurements:

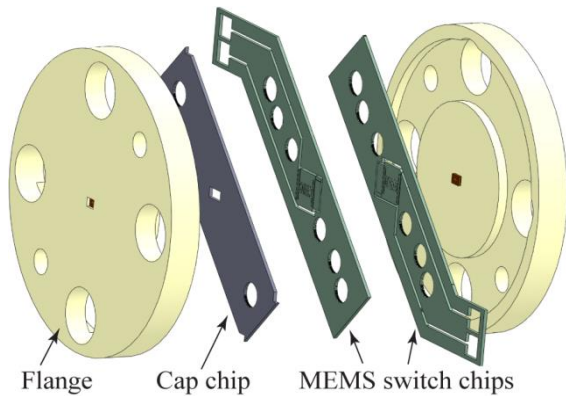


(a)



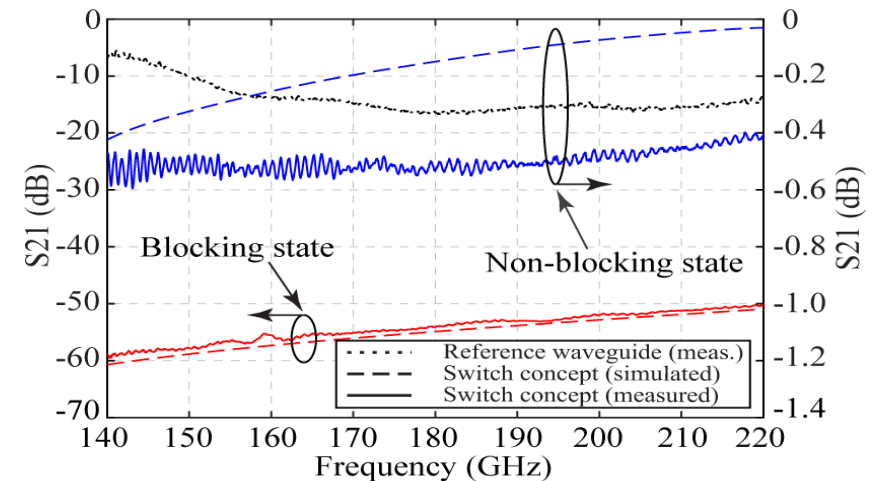
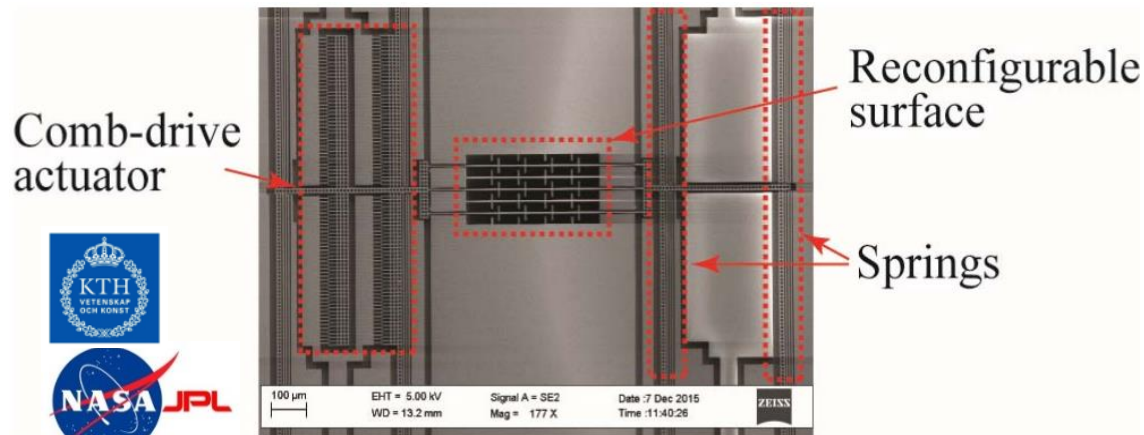
(b)

**Measured performance flange-to-flange:**  
**Insertion loss: < 0.6 dB**  
**Isolation: > 50 dB**  
**For whole band 140-220 GHz**



# MEMS waveguide switches by KTH (micro electro mechanical systems)

	Generation 1 60-70 GHz	Generation 2 500-750 GHz	Generation 3 140-220 GHz
Insertion loss	0.3-0.4 dB	2.5 dB	<0.6 dB
Isolation	30-40 dB	18-25 dB	>50 dB
On/off ratio	54	9	295

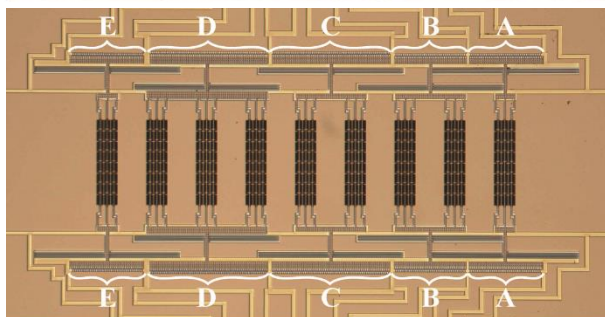
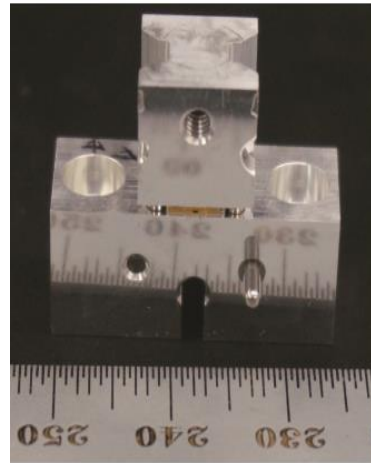
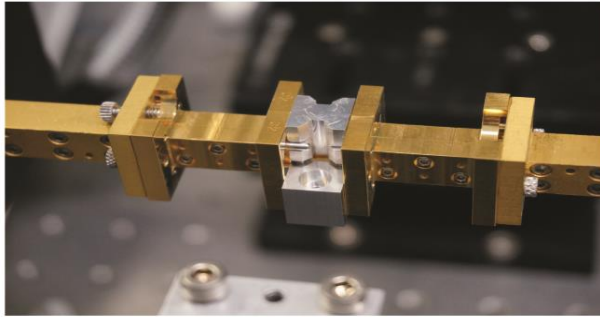


**500-750 GHz switch**

**140-220 GHz switch**

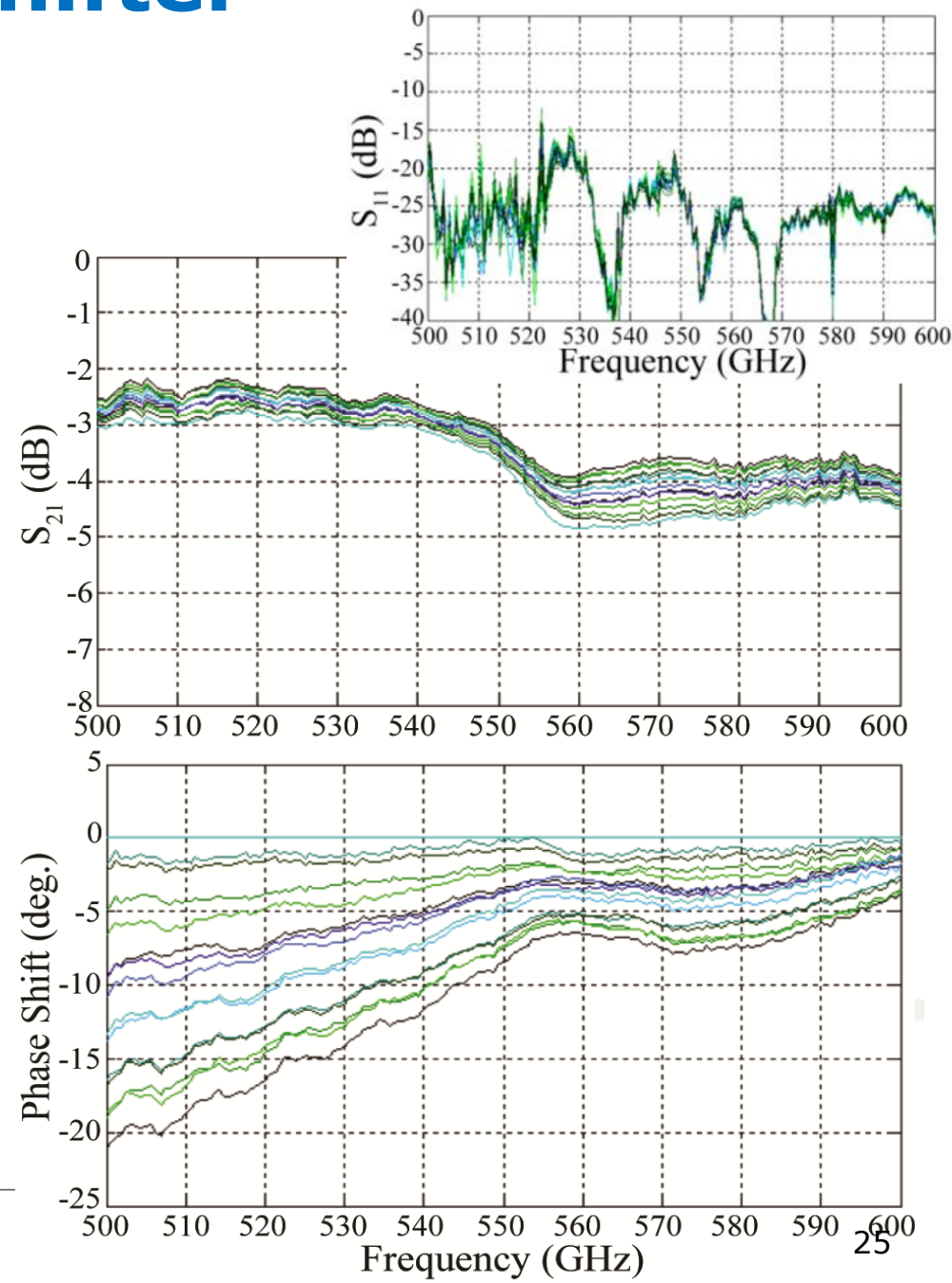


# 500-600 GHz 3.3 bit MEMS phase shifter



- First sub-mm-wave MEMS circuit
- First RF MEMS above 200 GHz
- First MEMS phase shifter above 110 GHz
- First MEMS waveguide component above 70 GHz

[IEEE IMS 2015; IEEE THzSciTec 2016]

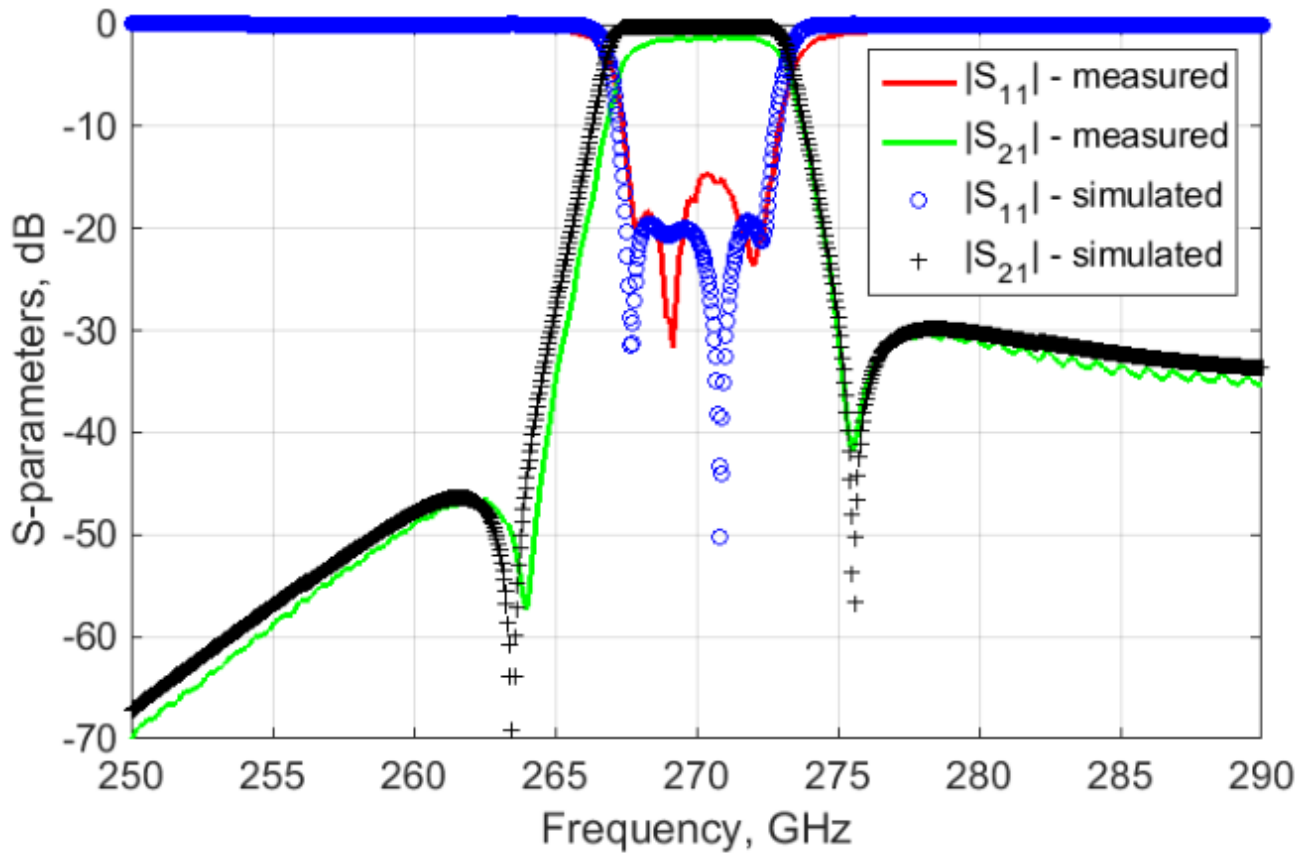




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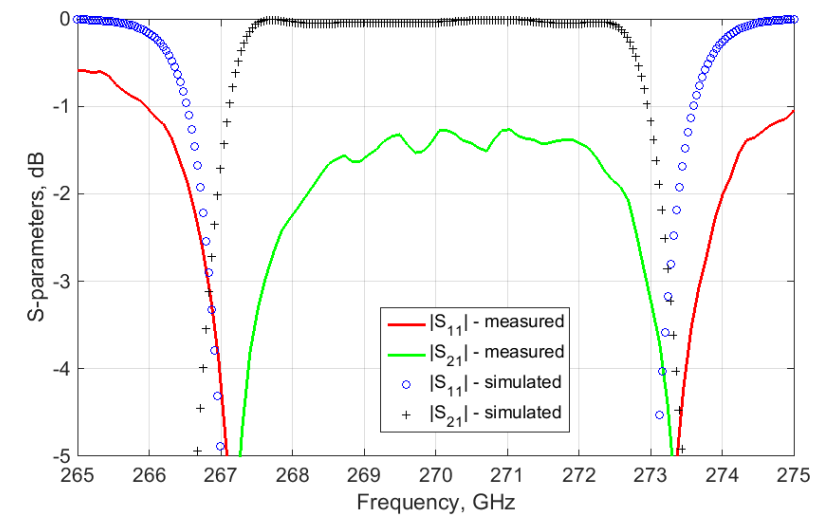
# *Ultra-high Q filters*

# KTH micromachined mm/sub-mm wave filter technology

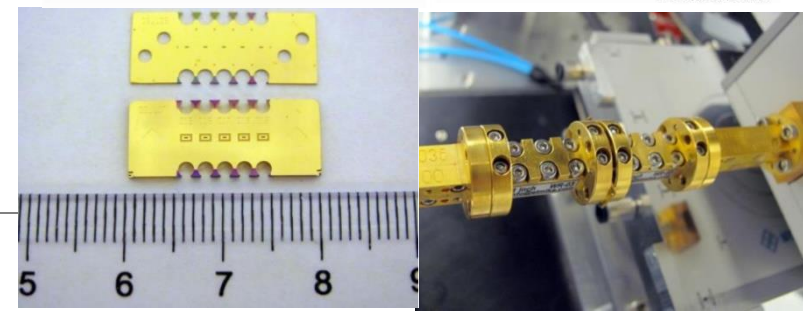
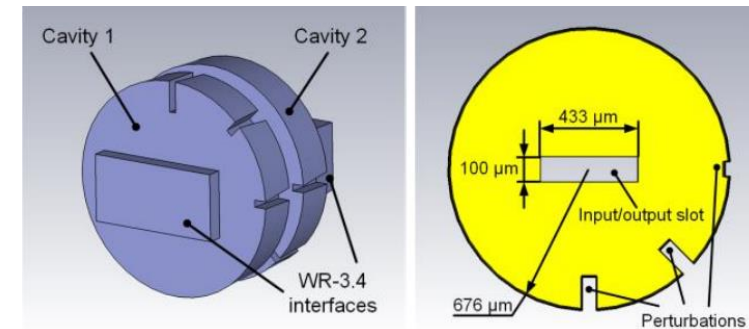


[IEEE IMS 2017]

- Best performance for any comparable filter design in any technology in this frequency band

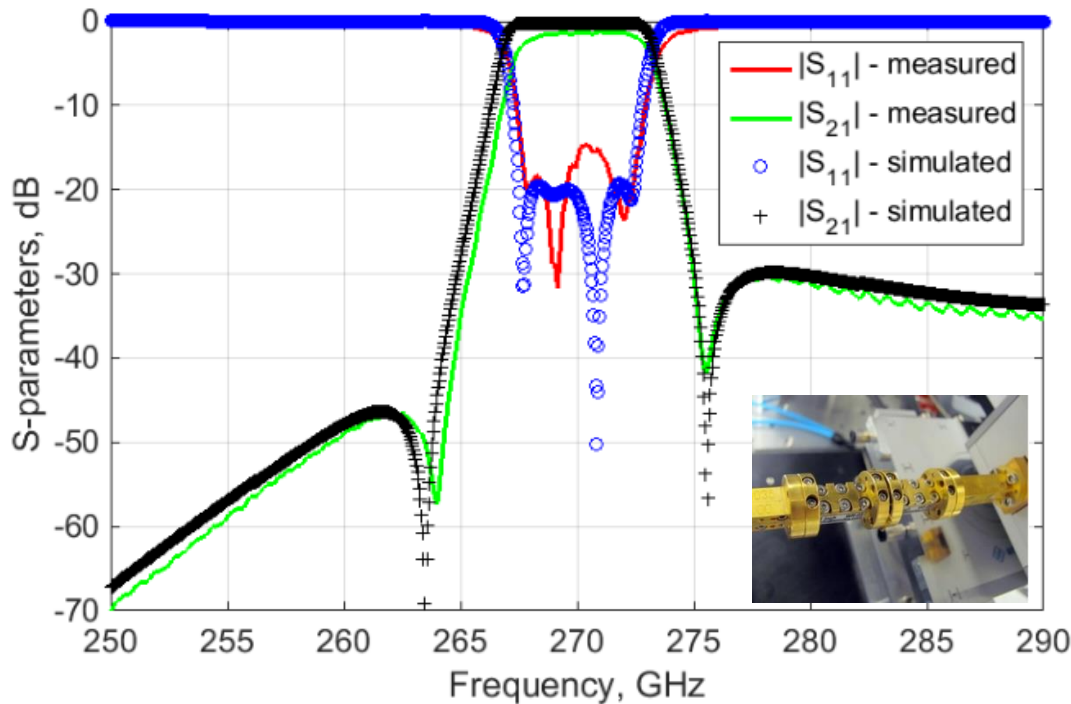


- $f_0 = 270$  GHz, **1.85% frac. BW** (267.5...272.5 GHz)
- avg. **IL=1.5dB** (best IL=1.25dB)
- avg. **RL=-18dB** (worst = 16dB)
- rejection: > 30 dB (<264, >276 GHz)



# KTH micromachined sub-THz filters: best Q-factors in any technology

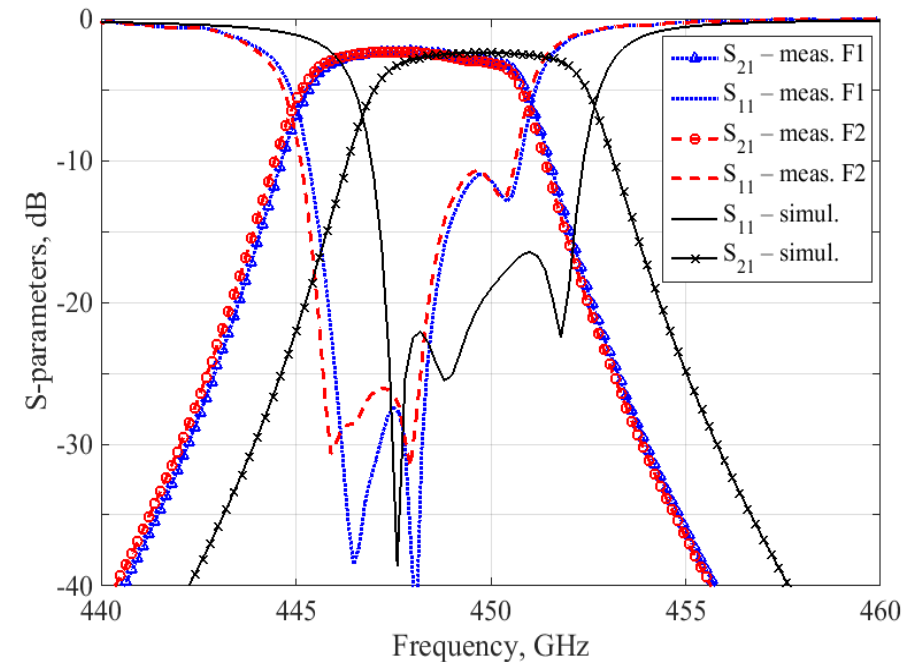
## 270 GHz, narrow-band:



- $f_0=270$  GHz, 4p2z
- 1.85% FBW
- IL=1.5dB, RL=-18dB
- $Q_{\text{unloaded}}=800$

[IEEE IMS 2017,  
IEEE TMTT 2019]

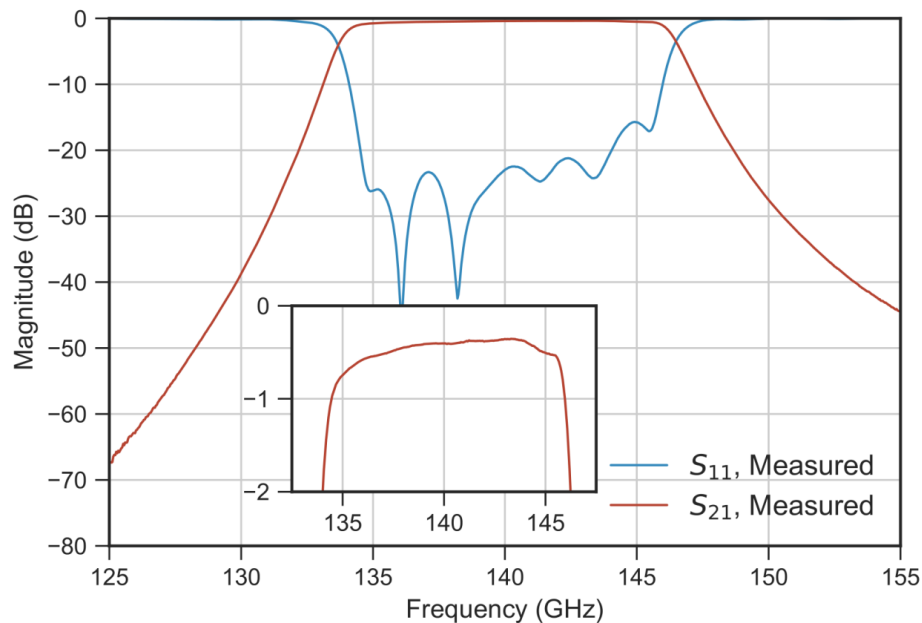
## 450 GHz, ultra narrow-band:



- $f_0=450$  GHz, 4p
- 1.00% FBW, IL=2.5dB
- $Q_{\text{unloaded}}=790$
- first 1%-BW filter at sub-mm wave frequencies! [IEEE TSTT,2019]

# KTH micromachined sub-THz filters: best Q-factors in any technology

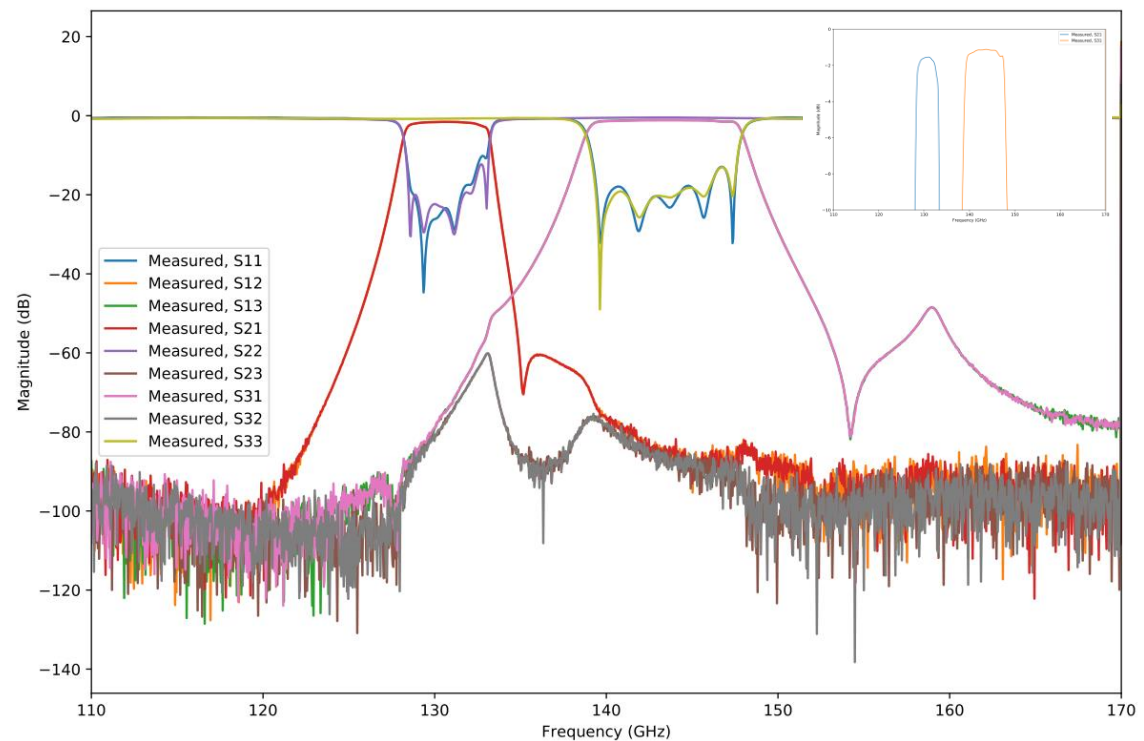
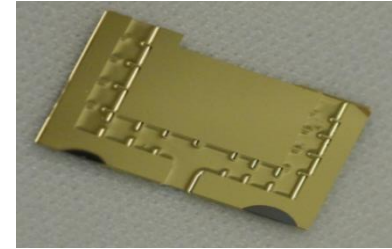
**Wide-band example:  
5.2% FBW, 141-148.5 GHz**



**<0.5dB IL,  $Q_{UL} \sim 1600$**

[IEEE IMS 2018]

**Telecom diplexer:  
141-148.5,  
129-134 GHz**



**<1.5dB IL, >60 dB isolation**



# What is next?

## Current micromachined filter development activities

Pushing current technology:

- 700 GHz filters with 1% fractional bandwidths

New generation technologies:

- W-band (75-110 GHz) filters with Q factors  $> 5000$
- 183 GHz narrow-band filter banks with Q factors of 5000
- Fabrication-tolerance insensitive filter geometries

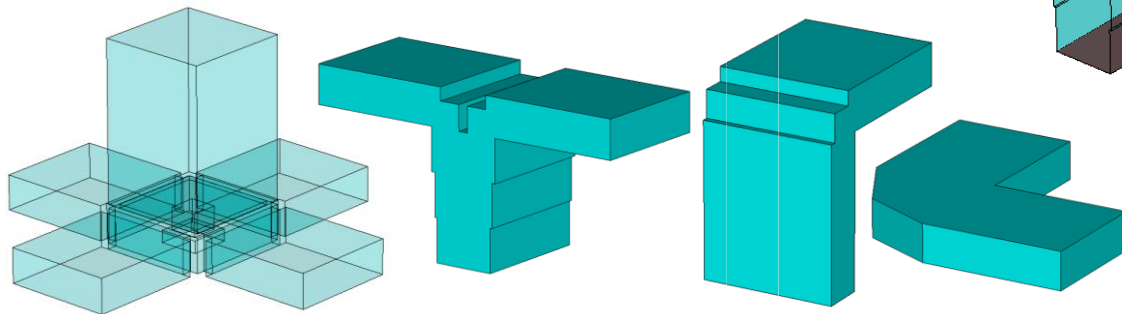
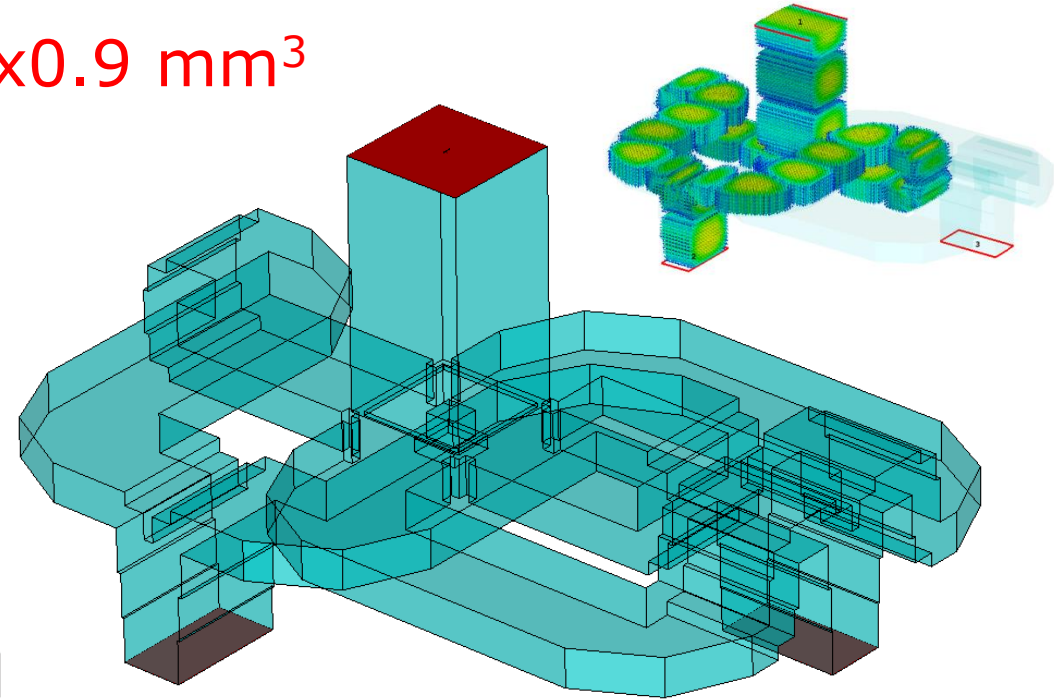
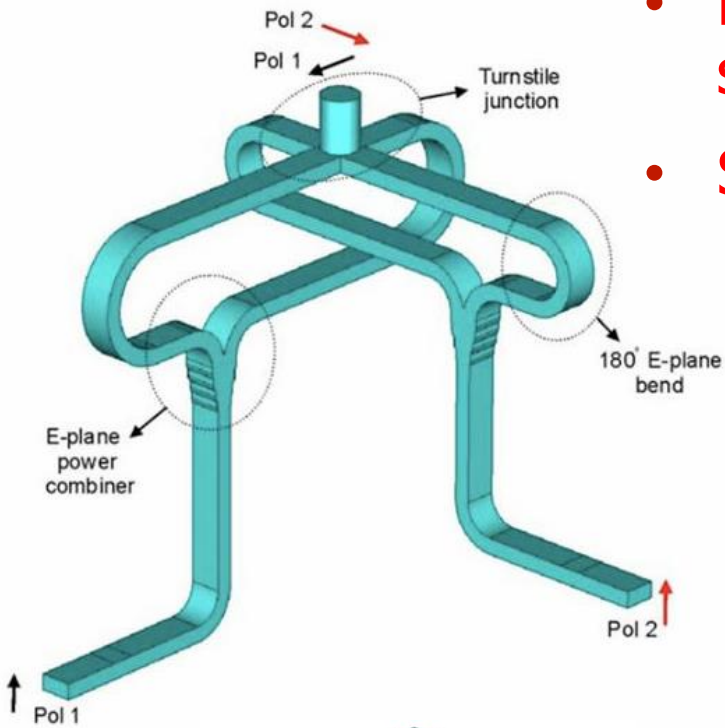


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# ***Micromachined ortho- mode transducer (OMT)***

# Micromachined orthogonal mode transducer (OMT) at 220-330 GHz

- First turnstile OMT above 110 GHz
- Micromachining enables microwave devices at so far unreachable frequencies!
- Size only  $5 \times 5 \times 0.9 \text{ mm}^3$

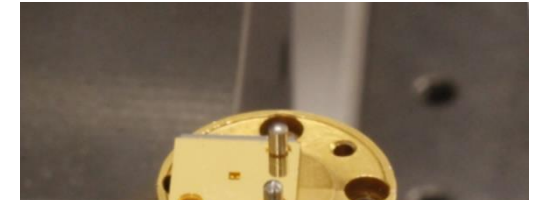


Combining very complex 3D geometries (9 etched Si layers)

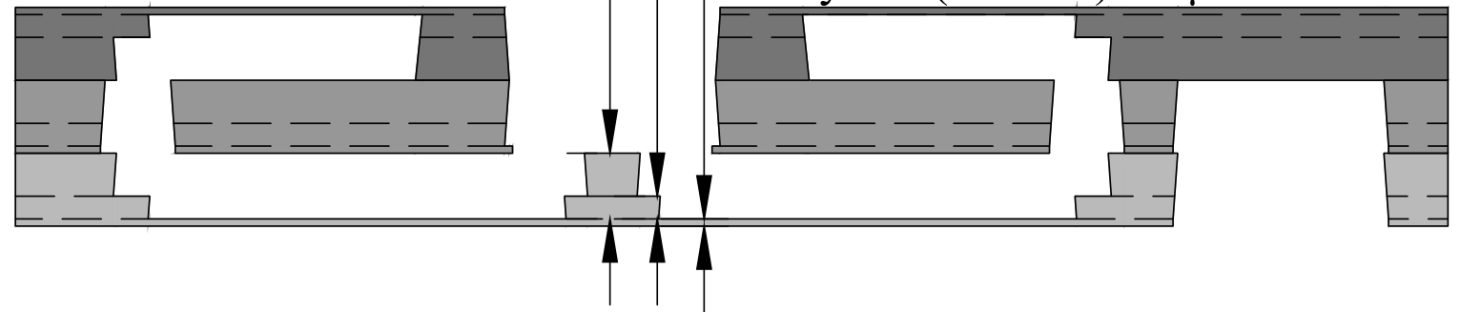


# Micromachined orthogonal mode transducer (OMT) at 220-330 GHz

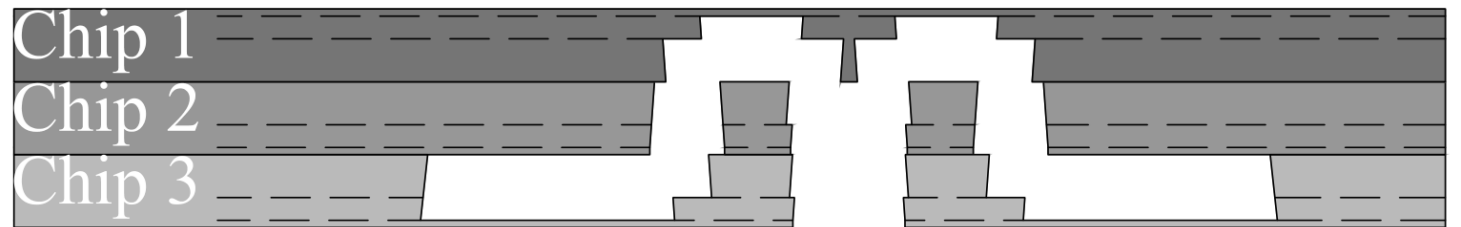
- First turnstile OMT above 110 GHz
- Enabled by micromachining
- 2 $\mu$ m alignment needed



Layer 3 (Mask 3): 275 $\mu$ m  
 Layer 2 (Mask 2): 95 $\mu$ m  
 Layer 1 (Mask 1): 30 $\mu$ m



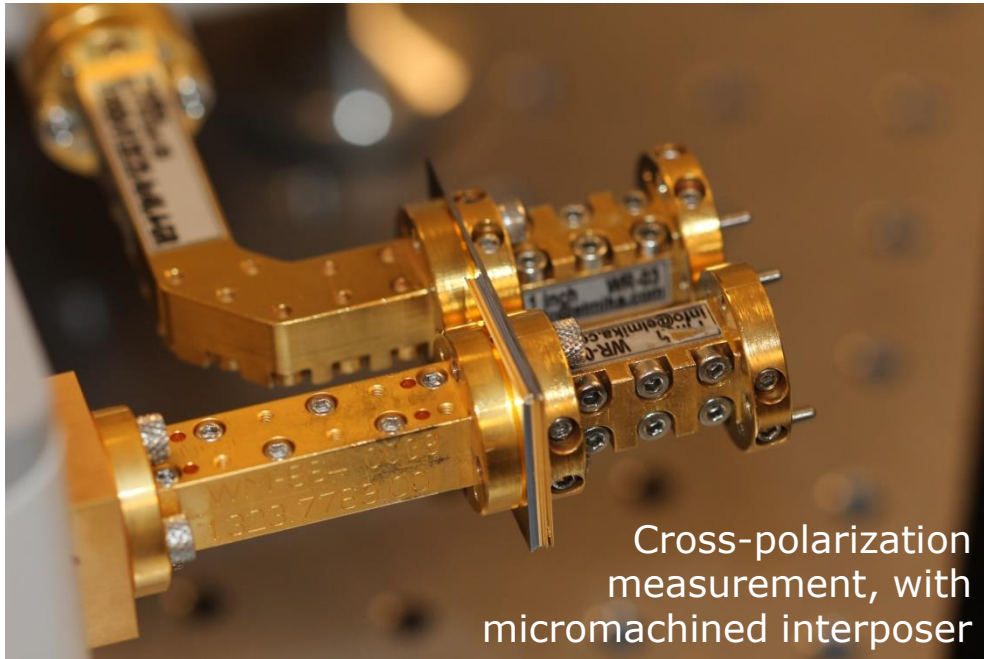
(a)



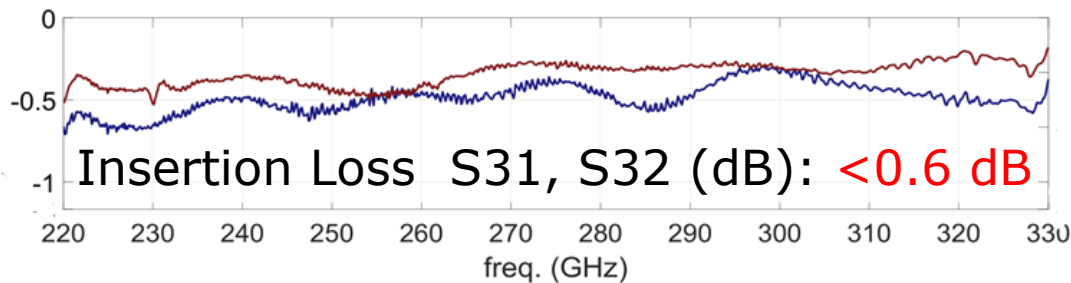
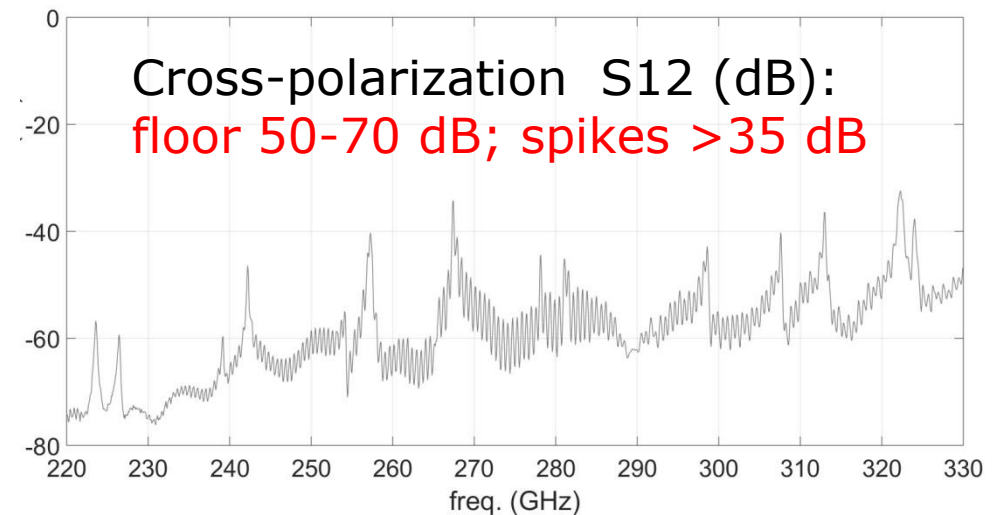
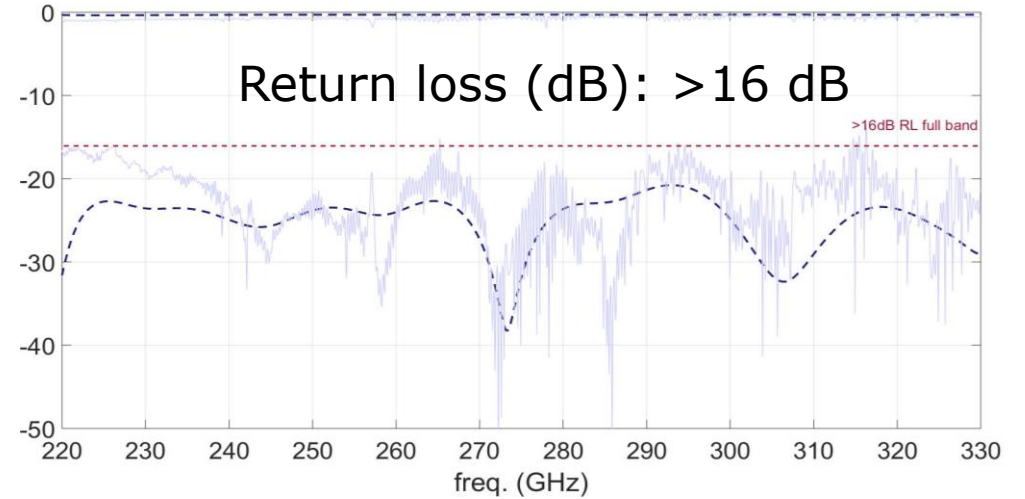
(b)

[IEEE IMS 2018]

# Micromachined orthogonal mode transducer (OMT) at 220-330 GHz



Cross-polarization measurement, with micromachined interposer





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***More complex systems:  
A micromachined TxRx  
integration platform for  
D-band point-to-point  
communication links***



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# Highly-integrated, micromachined D-band communication link

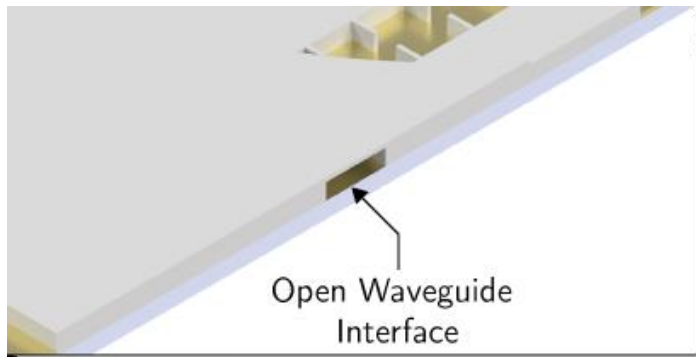
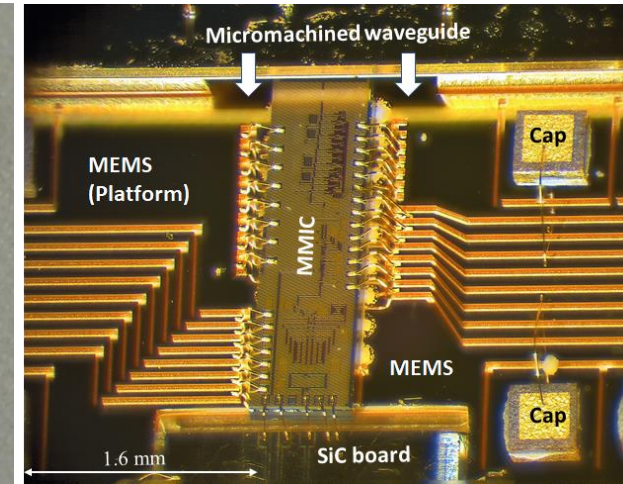
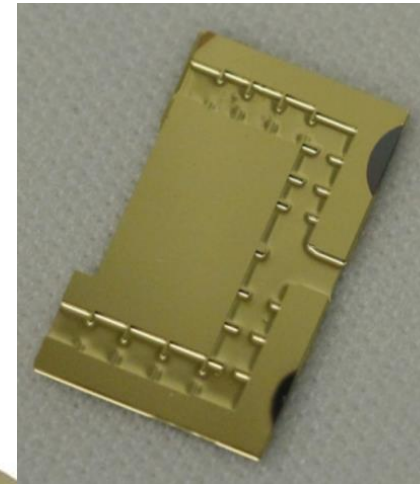


ERICSSON



ANTERAL

TECHNIKON



Open Waveguide Interface

2 cm

Silicon-Micromachined Integration Platform

Silicon-Micromachined Waveguide Diplexer

1.5 cm

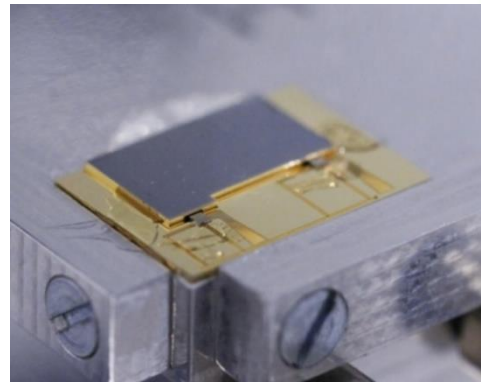
RF Routing

DC Routing

Slot Antenna

Bond Wires

MMIC



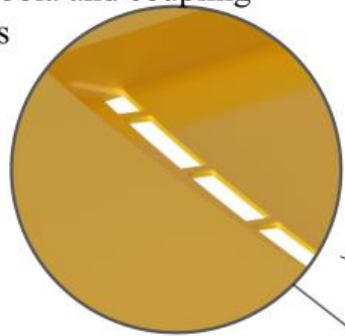


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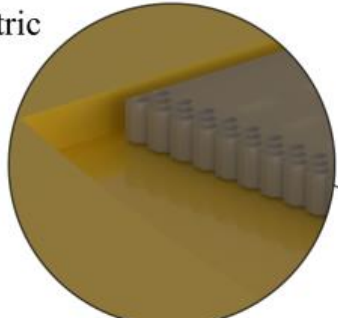
# **A micromachined high-gain leaky-wave antenna for beam steering at 220-300 GHz**

# Micromachined “pill-box” beam-steering antenna

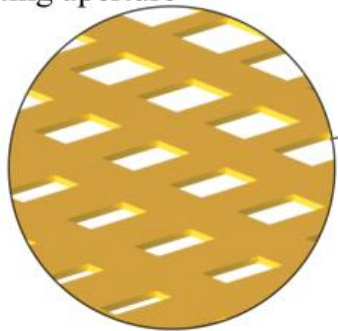
Parabola and coupling  
slots



Parabola and transition to  
dielectric  
PPW



Radiating aperture



24 mm

H-plane horn

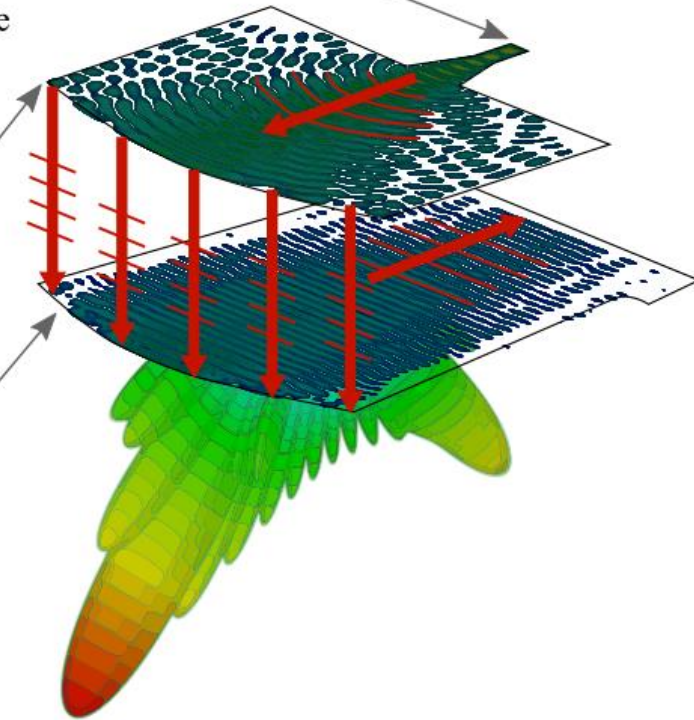
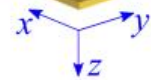
Input waveguide

Chip 3: Interface to standard  
waveguide flange

Chip 2: Pillbox

Teflon sheet

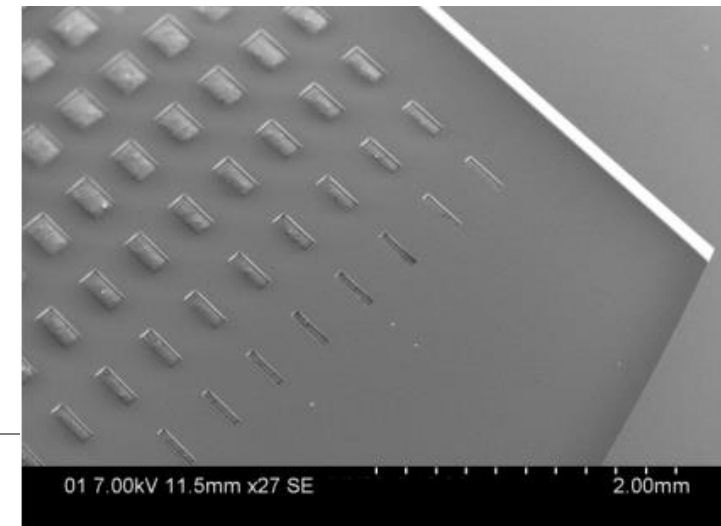
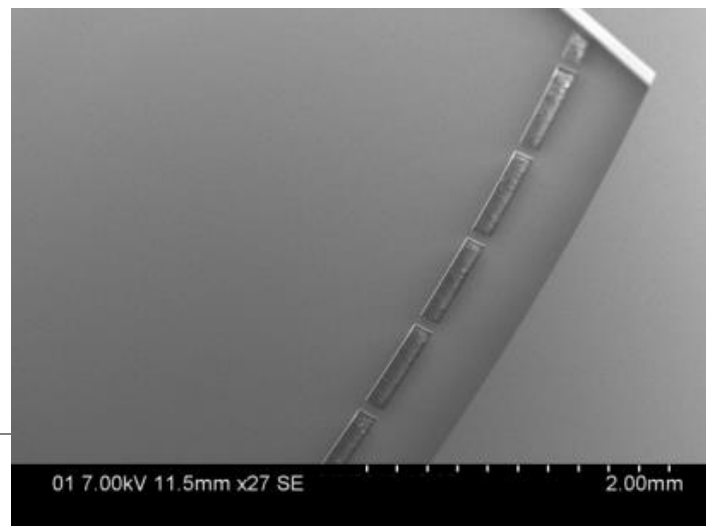
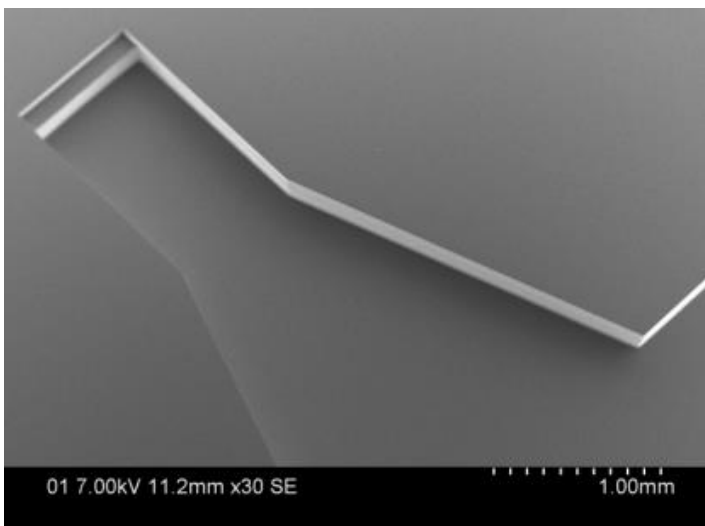
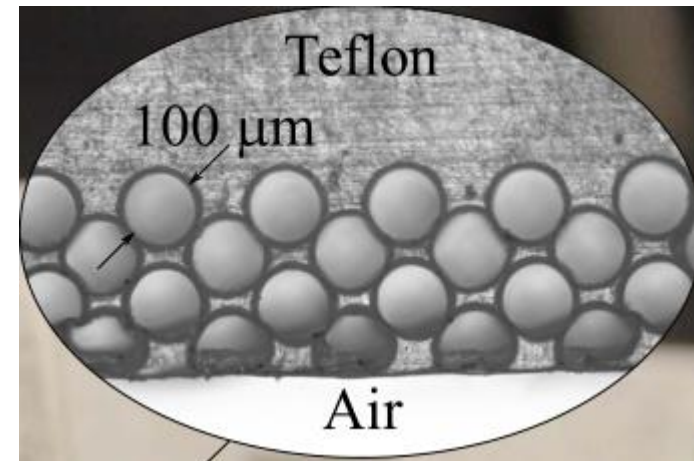
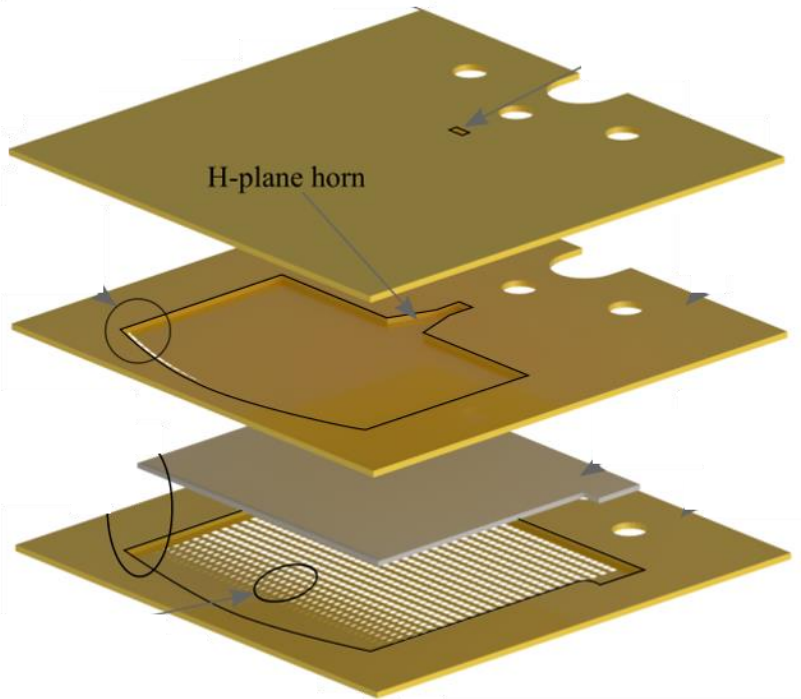
Chip 1: LWA



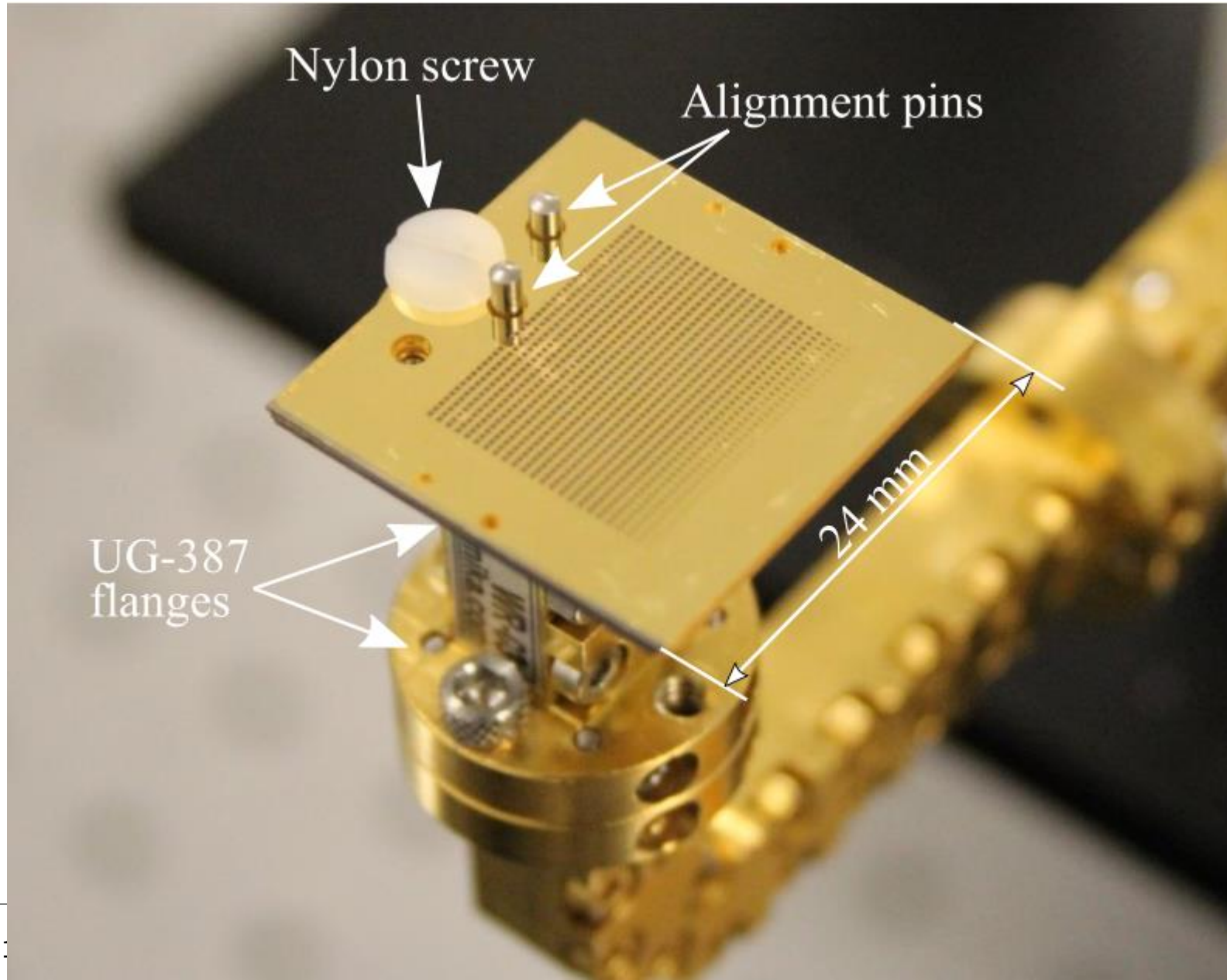
[IEEE T-AP 2019]

# Micromachined "pill-box" Leaky-wave antenna

[IEEE T-AP 2019]



# Micromachined “pill-box” beam-steering antenna

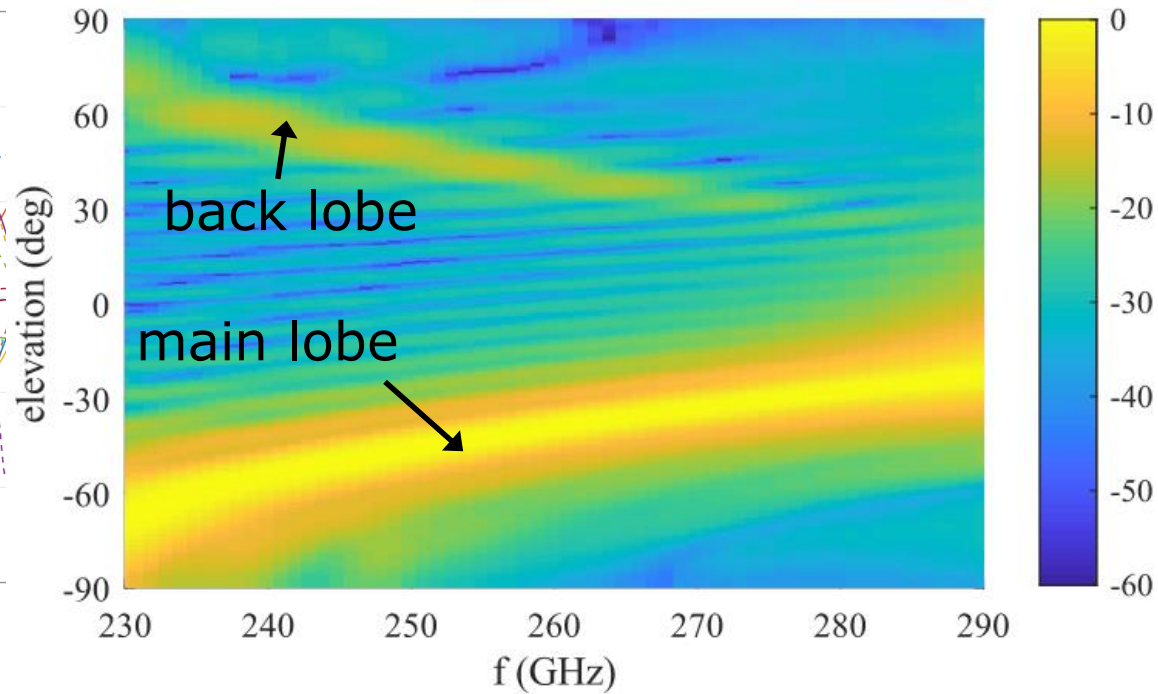
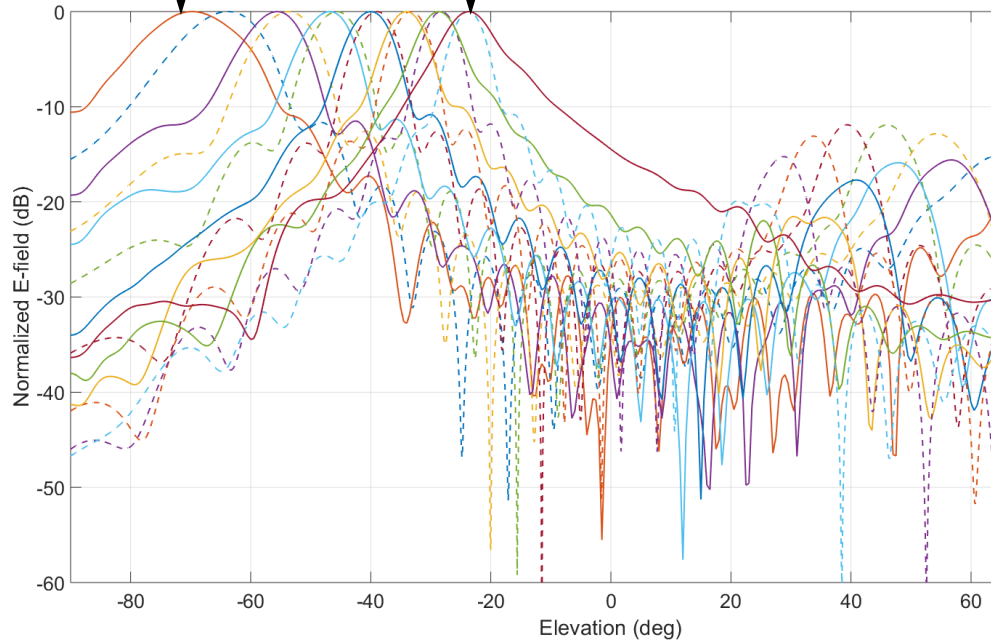


[IEEE T-AP 2019]



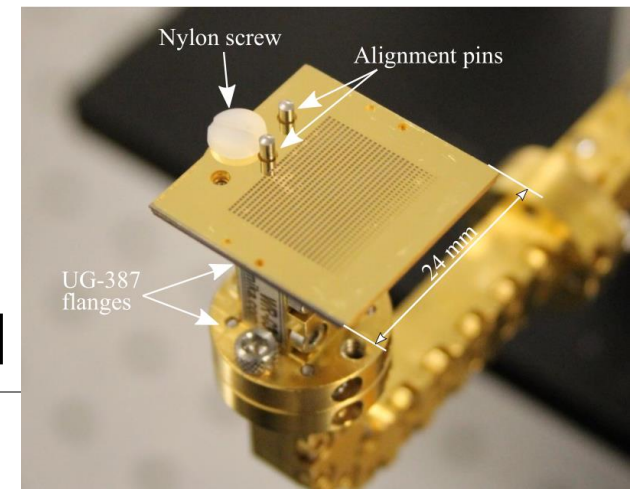
# Micromachined high-gain beam-steering leaky-wave antenna 220-290 GHz

240 GHz ↓ ... .. ↓ 290 GHz



- size: 24x24x0.9 mm<sup>3</sup>
- 220-300 GHz frequency sweeping  
=> 20°-75° scanning (55° field of view)
- measured gain: 28.5 dBi
- measured average HPBW: 7°

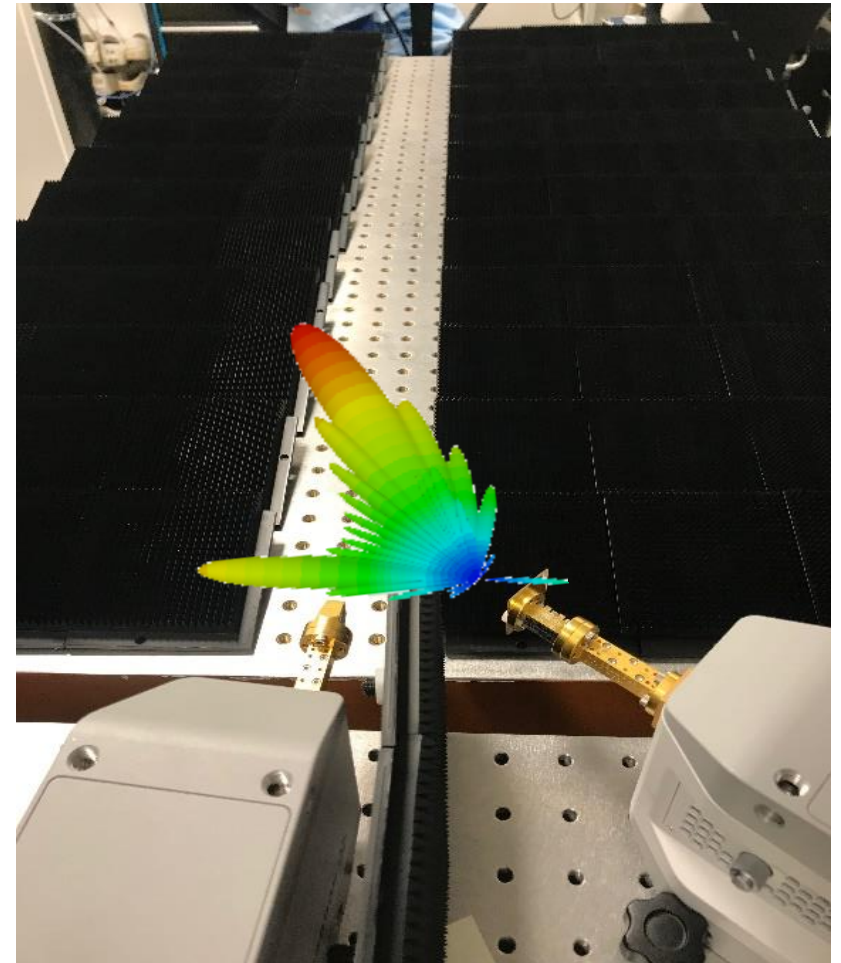
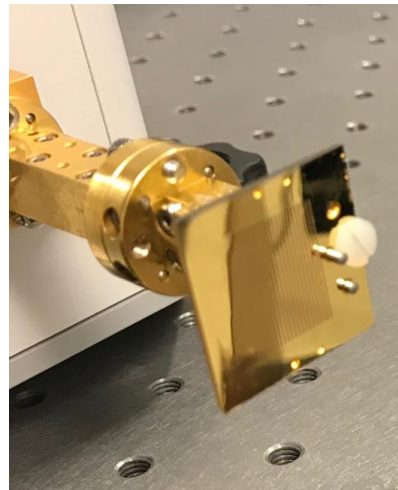
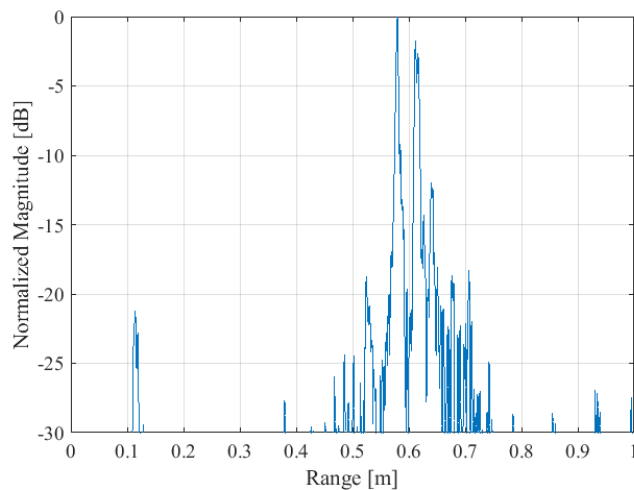
[IEEE T-AP 2019]



# Radar demonstrator based on micromachined beam-steering antenna at 220-300 GHz

## Micromachined radar front-end:

- 20 x 20 x 0.9 mm<sup>3</sup>
- 220..300 GHz freq. sweep, 20..75° scanning (55° FoV) 3.5-10° HPBW
- <0.5 cm range resolution *at* <10° angular resolution



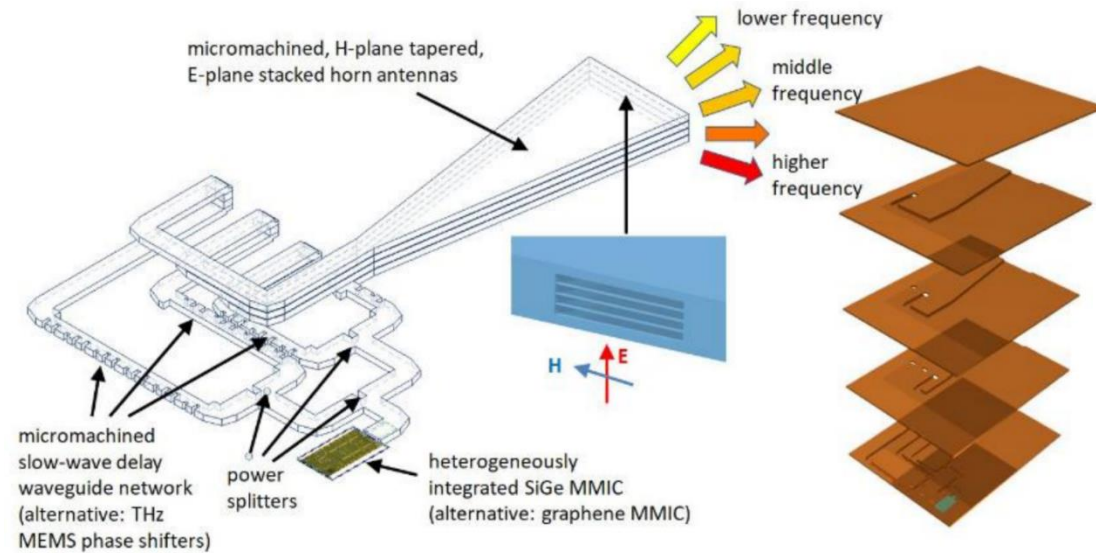
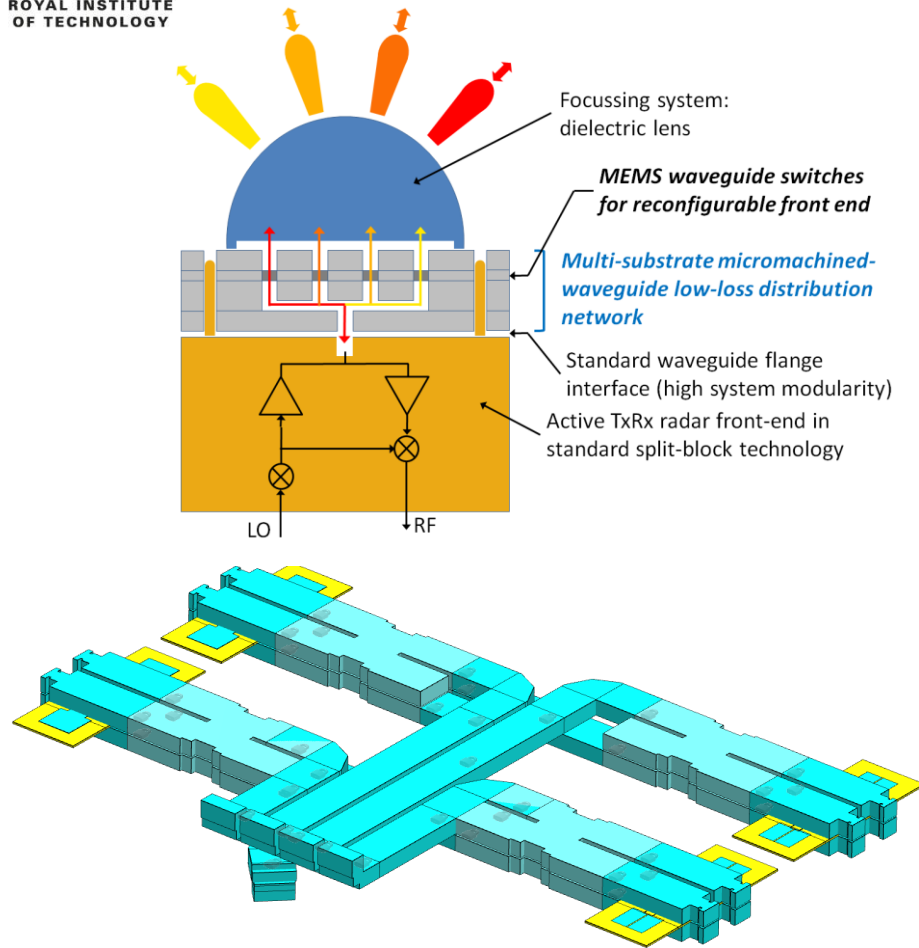
[IEEE IrMMWTHz 2019]



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# Beam-switching using MEMS waveguide switches

# THz MEMS for radar beam steering



## 238-248 GHz car radar

- micromachined beam-steering front-end
- intelligent beam-shaping

## MEMS-switched 340 GHz industrial radar:

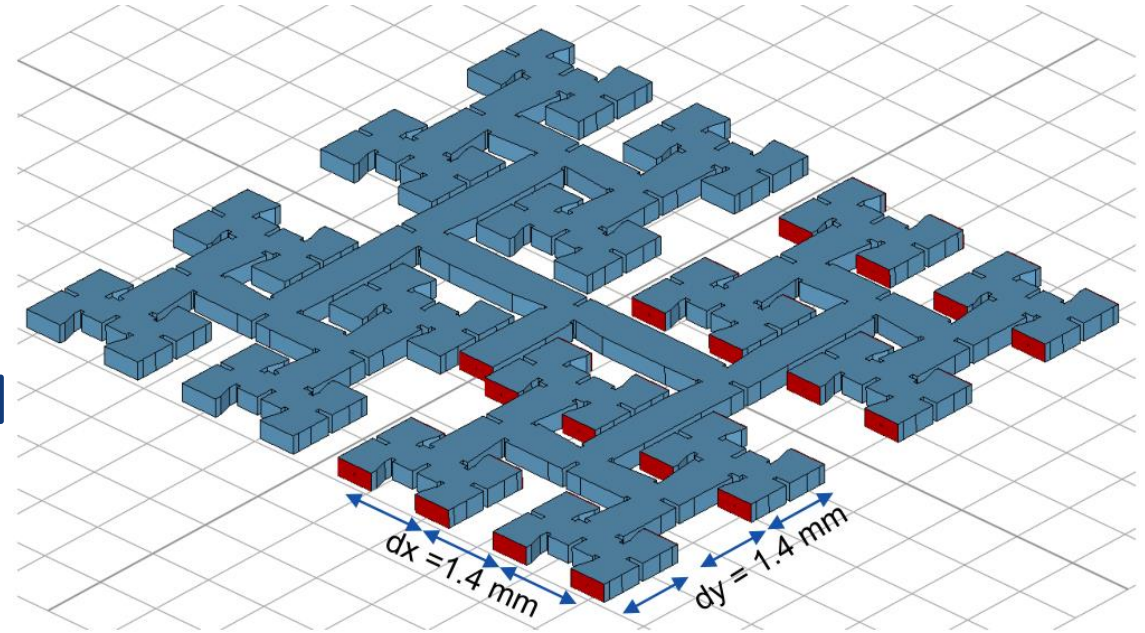
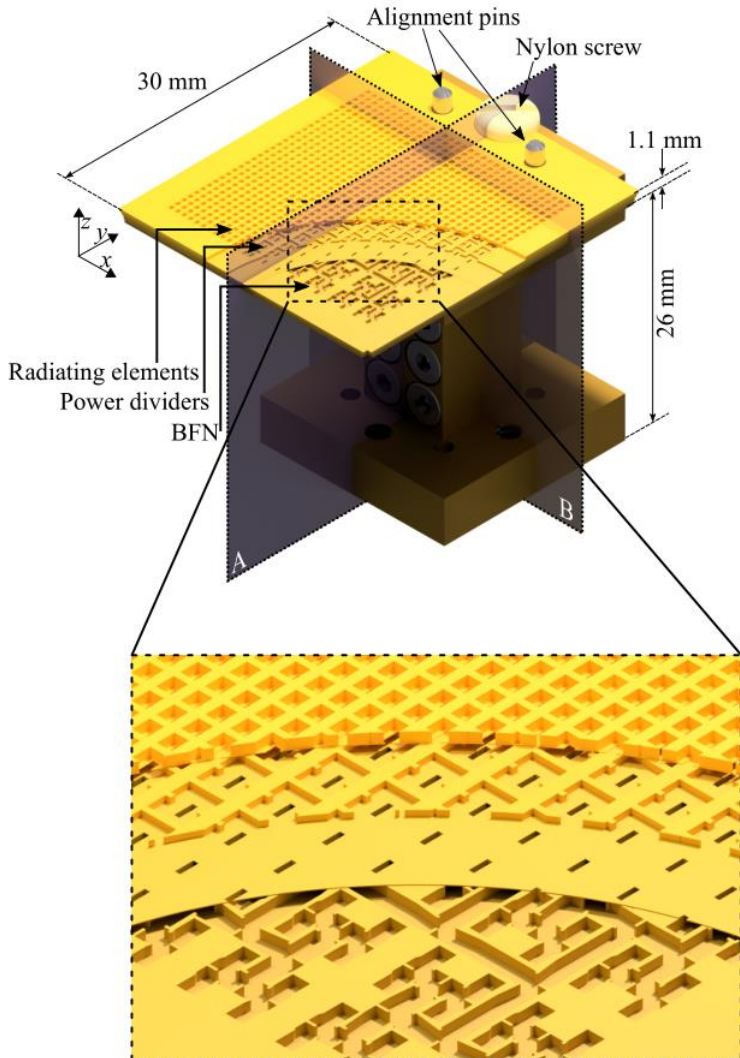
- 340 GHz, 30 GHz BW, 4x1 and 4x2 arrays
- using MEMS Waveguide switches:
  - <0.6dB IL, >50 dB ISO



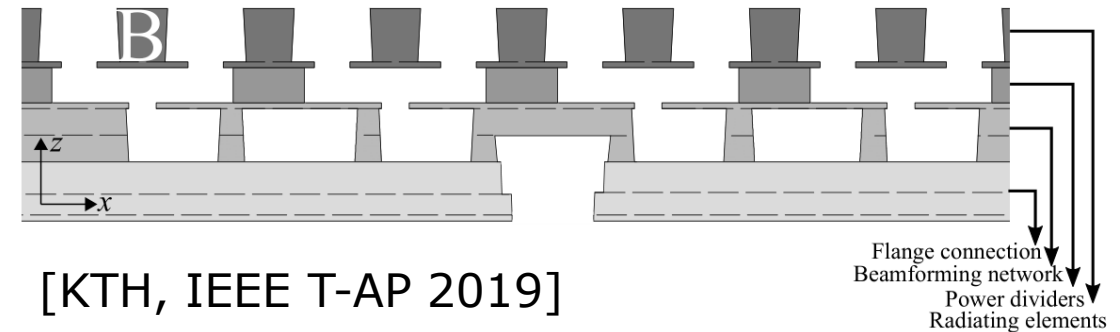
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# Ultra-compact, corporate-fed, large-scale antenna arrays at 300-400 GHz

# Micromachined super-compact, super high-gain antennas

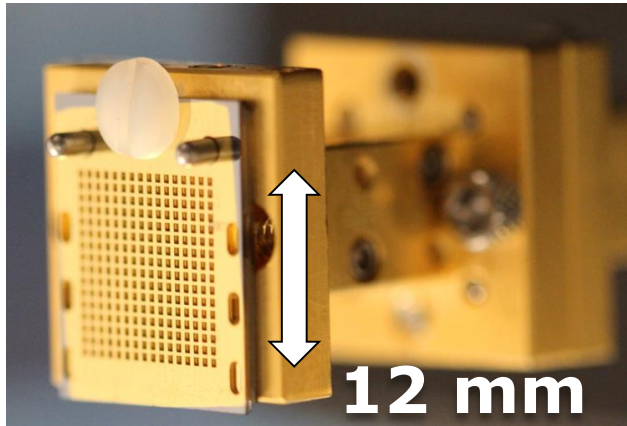


Single-layer feeding network to 2x2 sub-arrays => 16x16 antenna array



[KTH, IEEE T-AP 2019]

# Micromachined super-compact, super high-gain antennas



**16x16 antenna array: 256 elements**

**320-400 GHz, 80 GHz BW**

Directivity: 33.5 dBi

Gain: 32.8 dBi

Loss: <0.8 dB

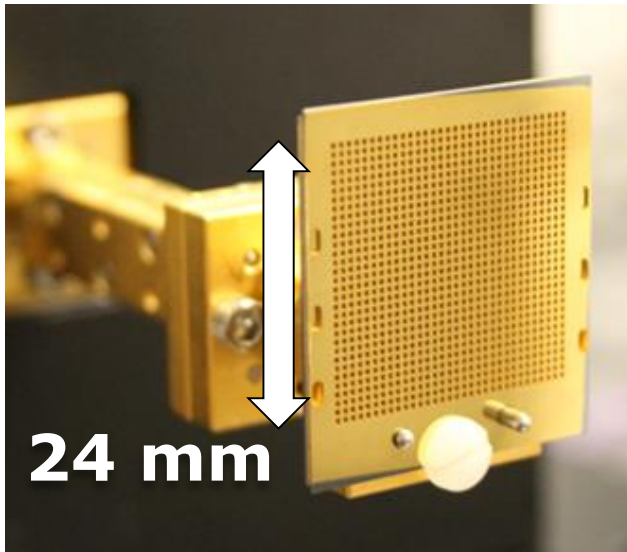
HPBW: <4.2°

Radiation efficiency: >82%

Avg. RL in band: 15 dB

Size:

12x12x1.1mm<sup>3</sup>



**32x32 antenna array: 1024 elements**

**320-400 GHz, 80 GHz BW**

Directivity: 39.7 dBi

Gain: 38.2 dBi

Loss: <1.6 dB

HPBW: <2°

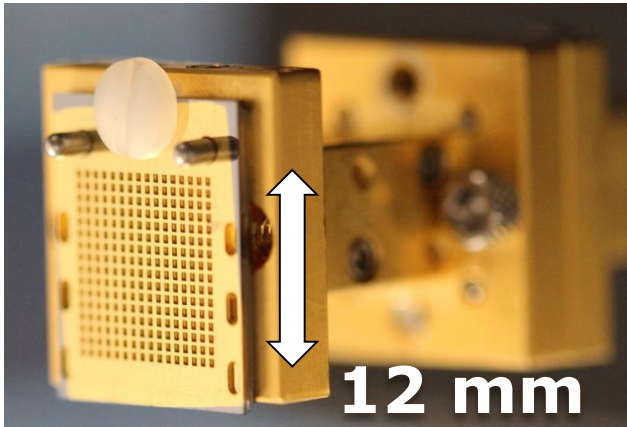
Radiation efficiency: >60%

Avg. RL in band: 15 dB

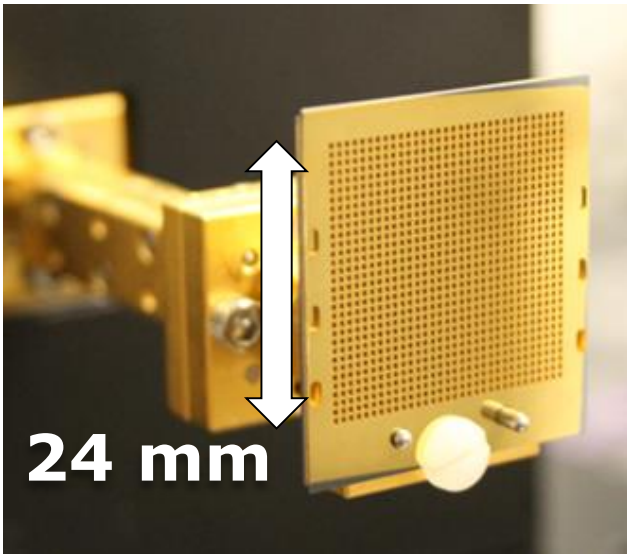
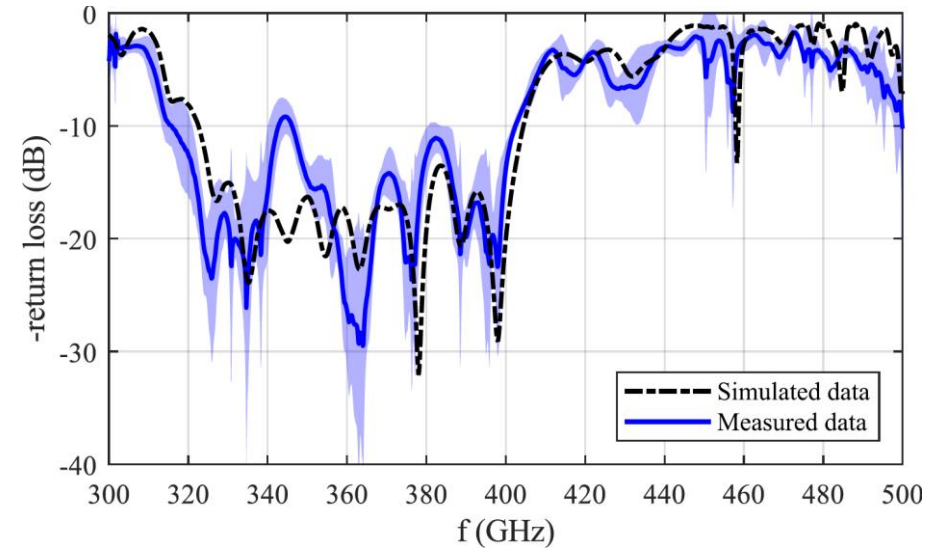
Size:

24x24x1.1mm<sup>3</sup>

# Micromachined super-compact, super high-gain antennas

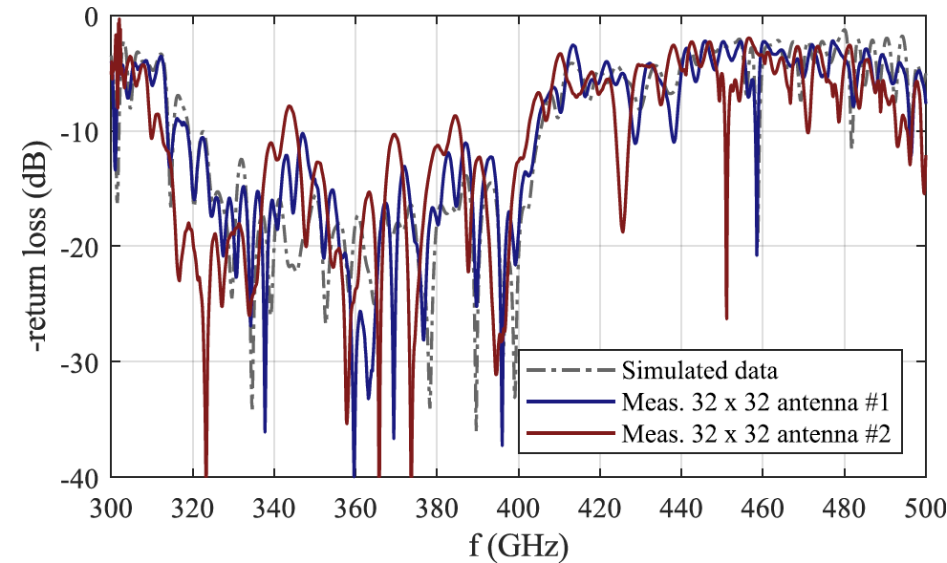


16x16 antenna array  
320-400 GHz



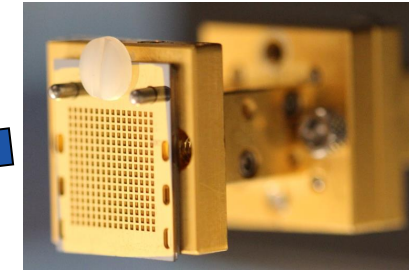
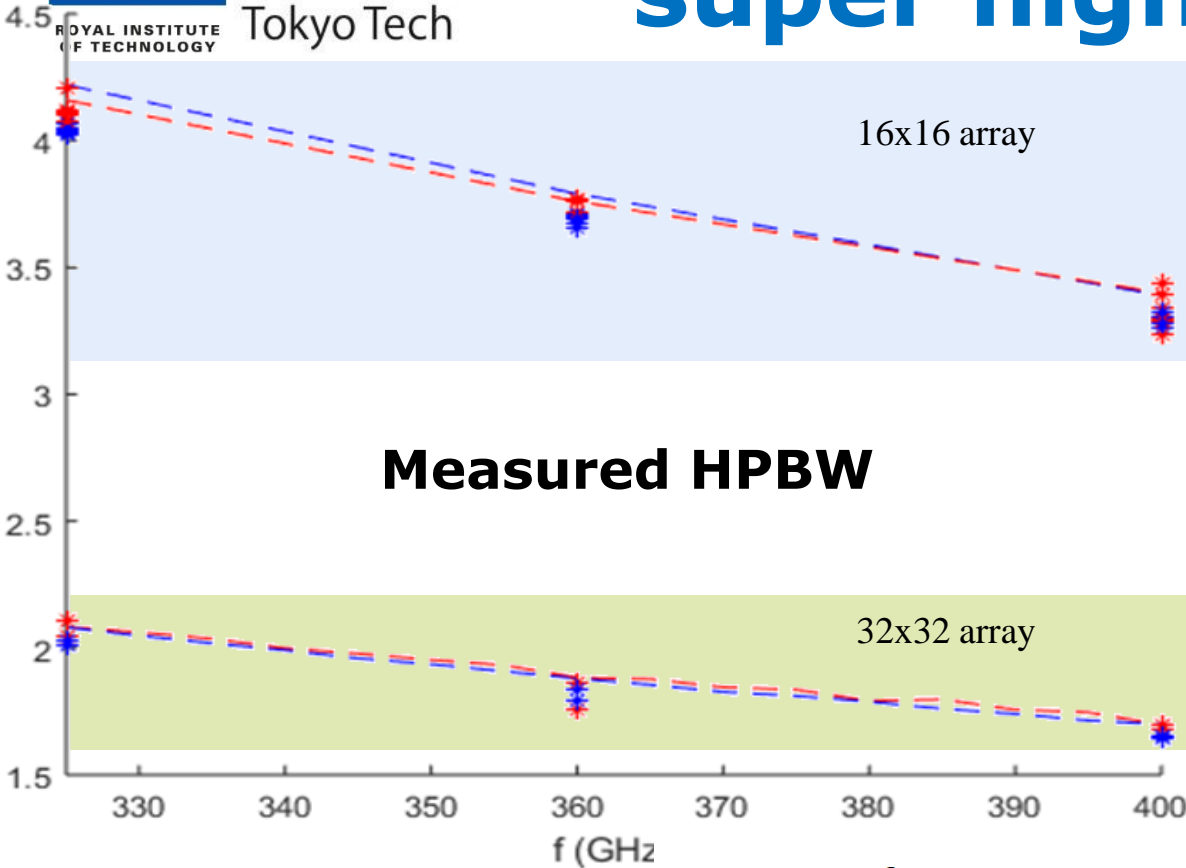
32x32 antenna array  
320-400 GHz

## Measured RL: 80 GHz BW

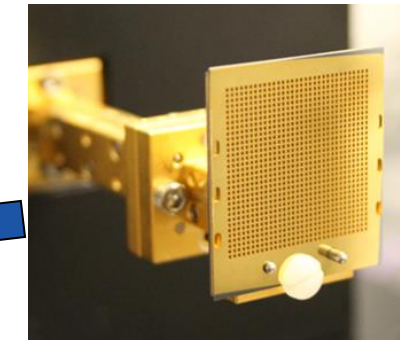




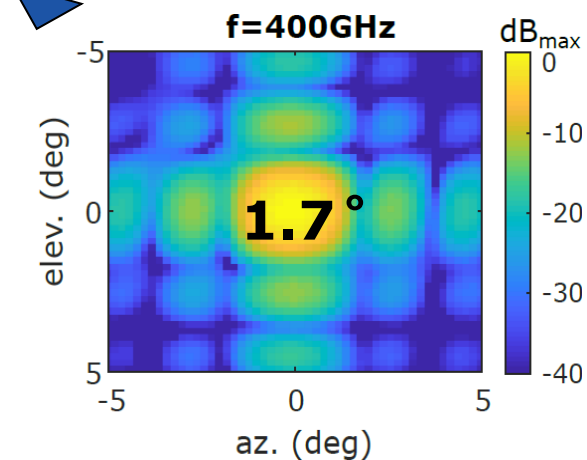
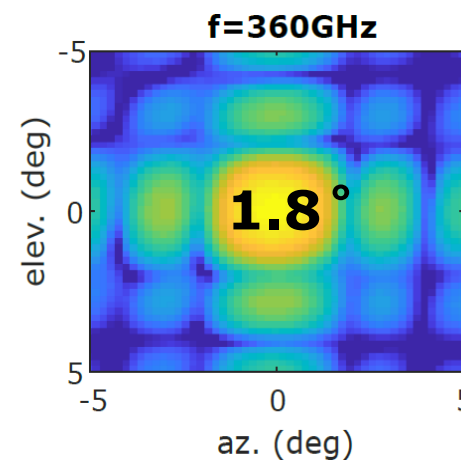
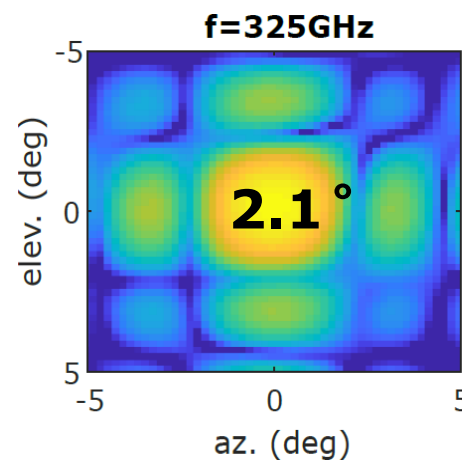
# Micromachined super-compact, super high-gain antennas



16x16 antenna array



32x32 antenna array

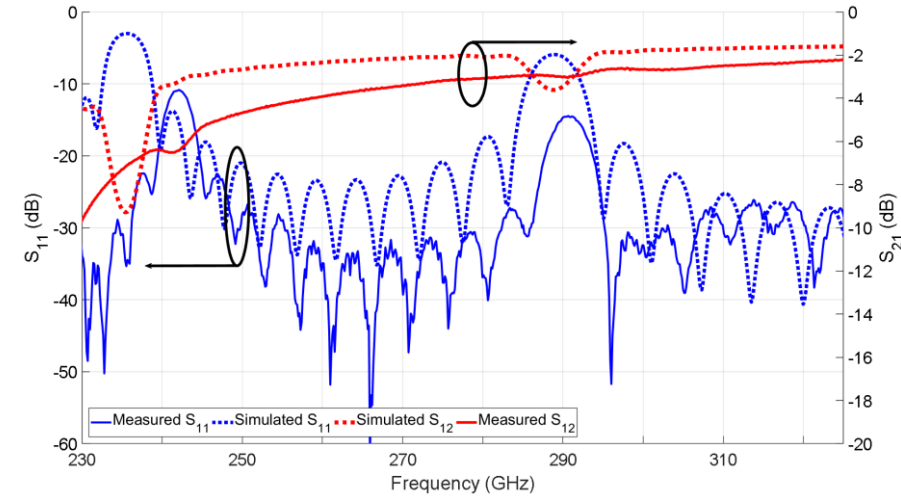
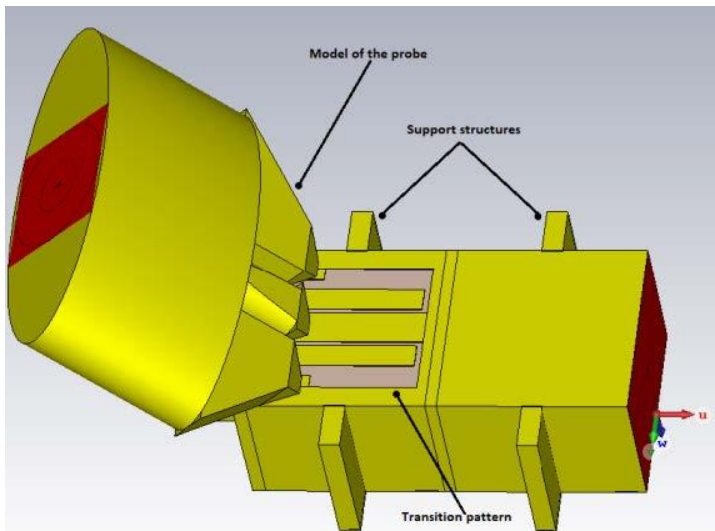
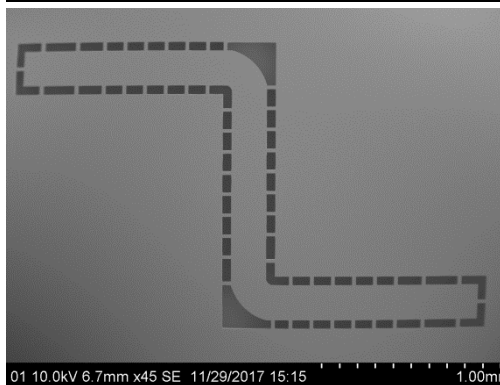
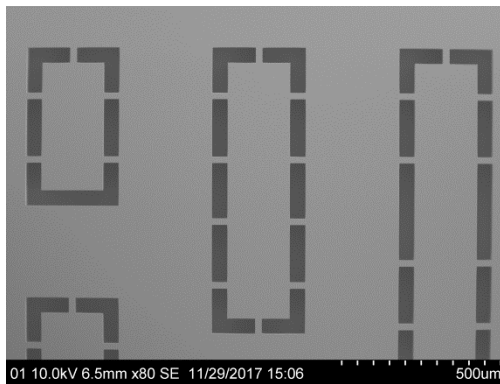
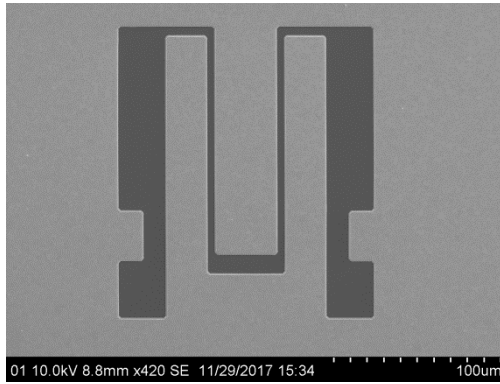
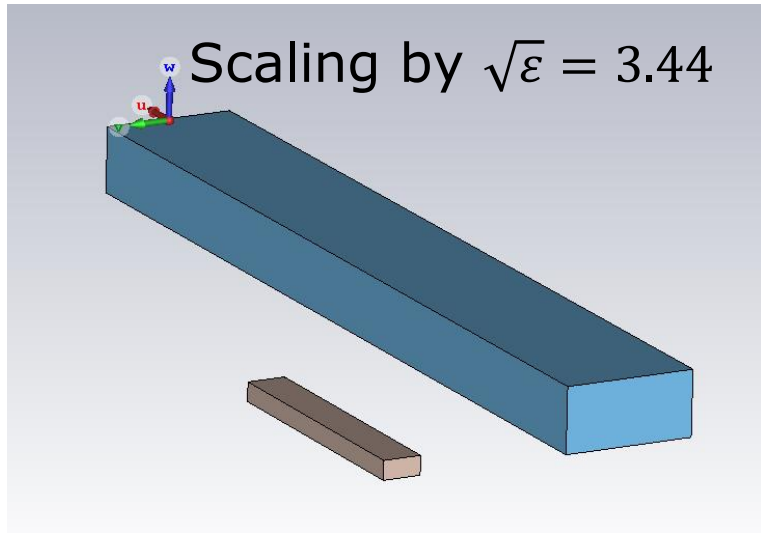




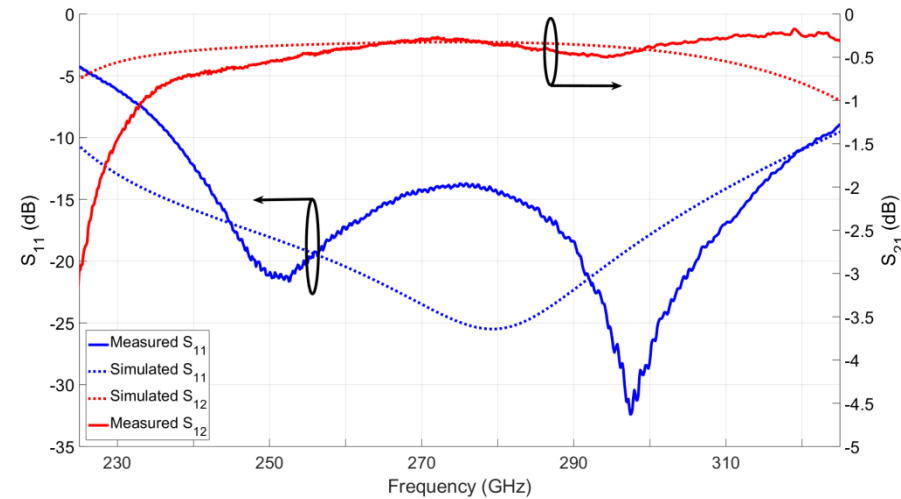
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# *Dielectric waveguides*

# Silicon-core metal-WG 220-330 GHz

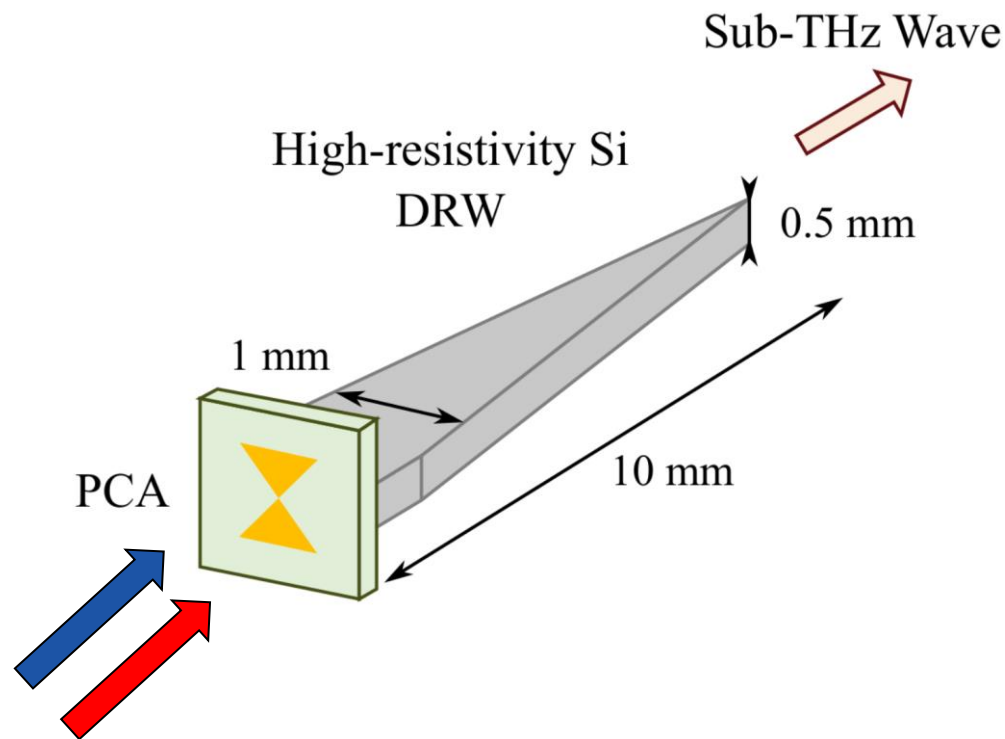


WG line  $IL = 0.14 \text{ dB}/\lambda_g$



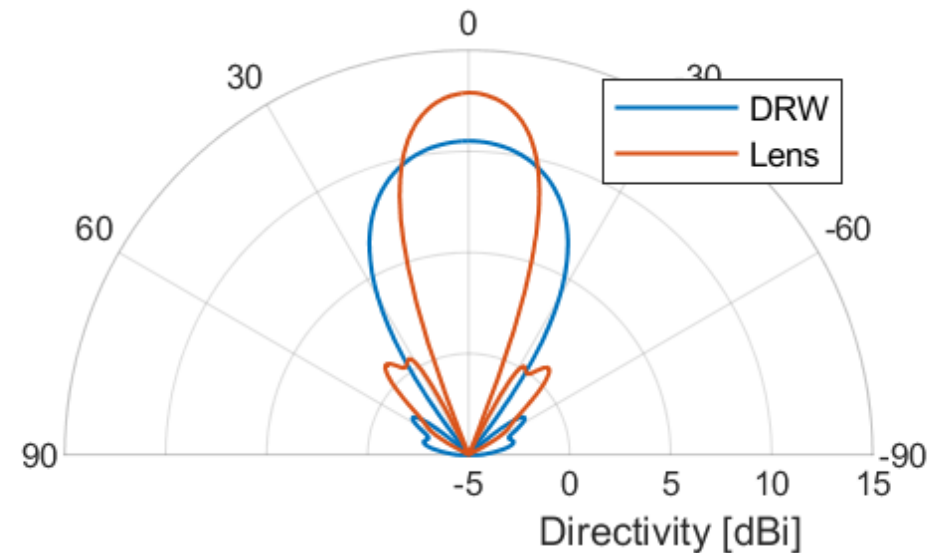
CPW transition  $IL < 1 \text{ dB}$

# Dielectric rod waveguides (DRW) antenna with integrated photonics/microwave converter



Dual-line photonic  
signal, 1.5  $\mu\text{m}$

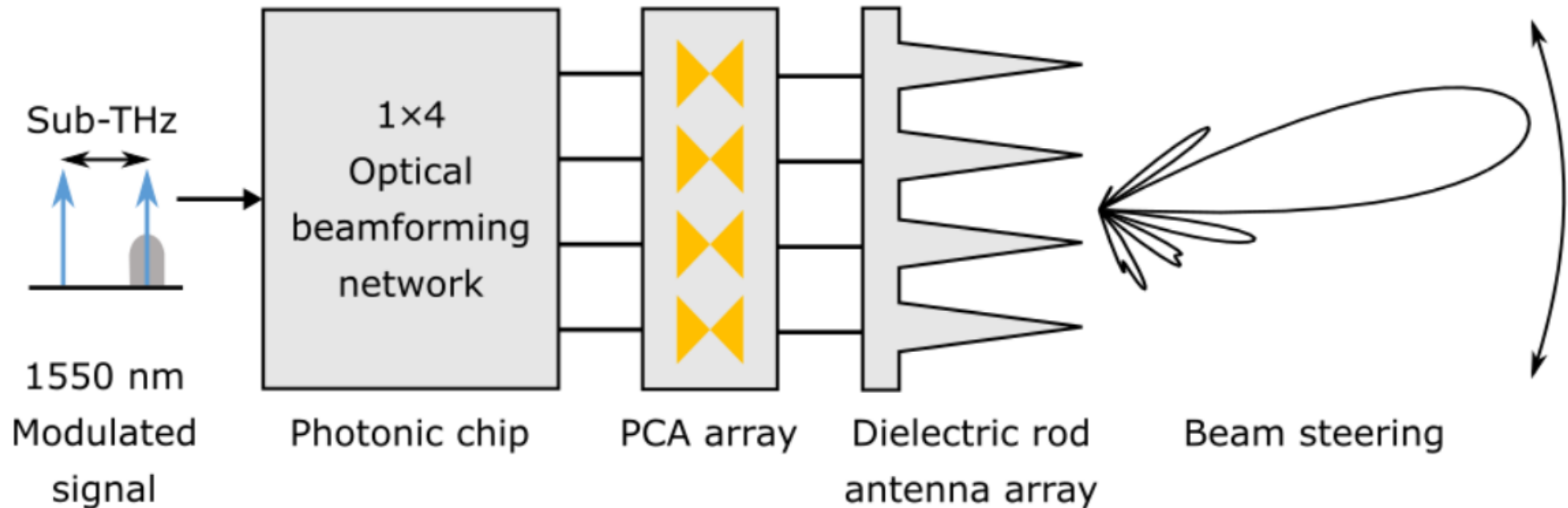
PCA ... photoconductive antenna: bow-tie  
antenna with InGaAs photodiode



DRW antenna (14.7 dBi directivity)  
compared to lens

[KTH, unpublished]

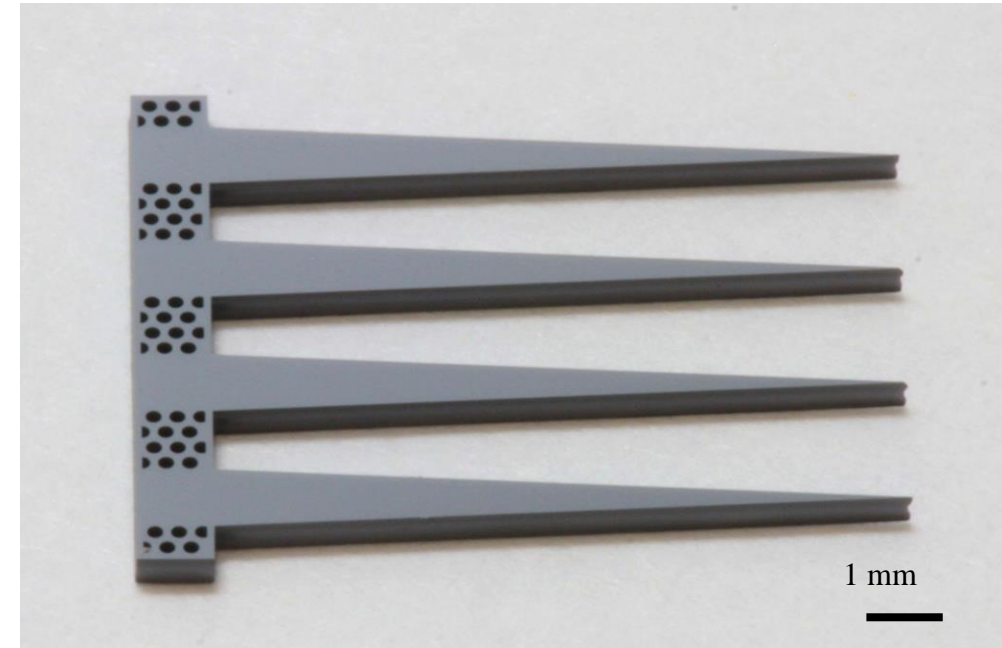
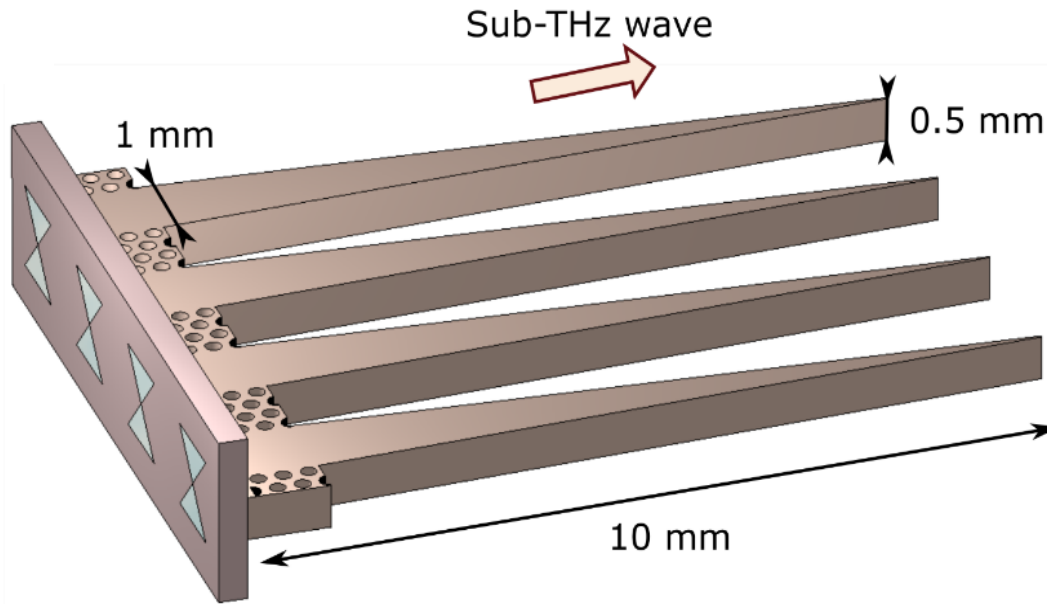
# Dielectric rod waveguides (DRW) antenna arrays with integrated PCAs for beam steering



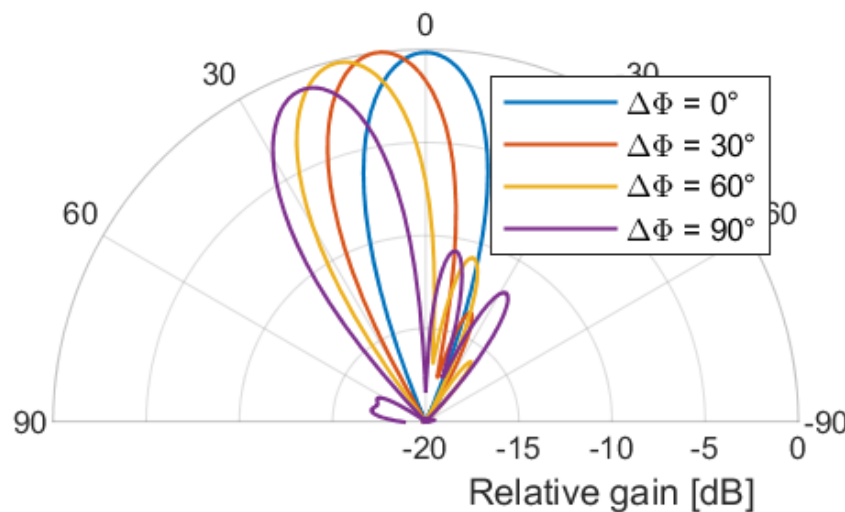
PCA ... photoconductive antenna: bow-tie antenna with InGaAs photodiode

[KTH, unpublished]

# Dielectric rod waveguides (DRW) antenna arrays with integrated PCAs for beam steering



Silicon-micromachined prototype for 85 GHz 4x1 array



[KTH, unpublished]



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# Conclusions

- micromachining: an enabling technology for high performance, miniaturized mmW and sub-mmW systems:
  - Very small and accurate feature size and surface roughness
  - High product uniformity, volume manufacturable
  - Integrated micromechanics => near-ideal reconfigurability
- KTH has shown many high-performance devices: filters, duplexers, phase shifters, switches, couplers, OMT

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Joachim Oberhammer

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- VINNOVA Smartare Elektroniksystem

